

FIG. 1D

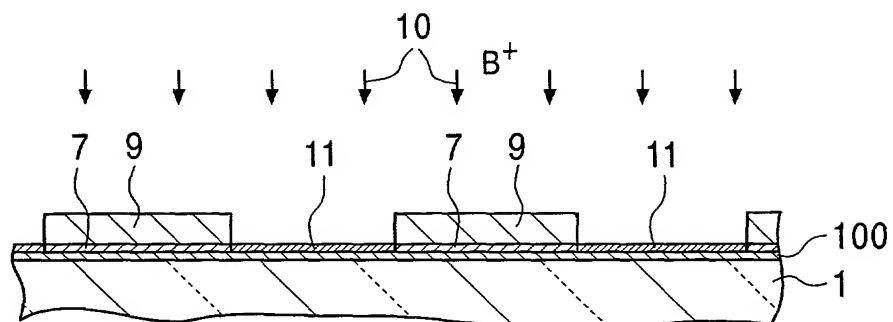


FIG. 1E

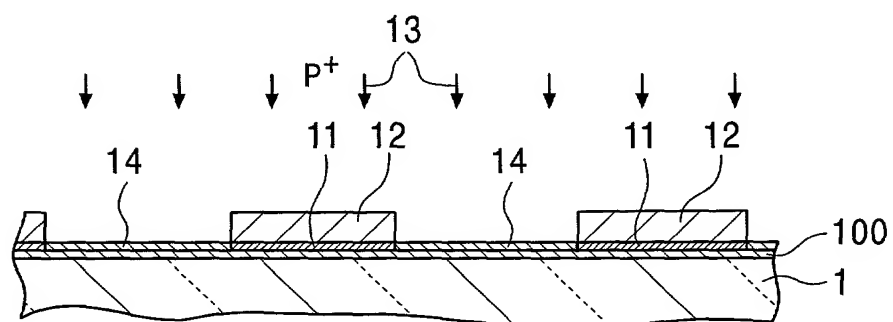


FIG. 1F

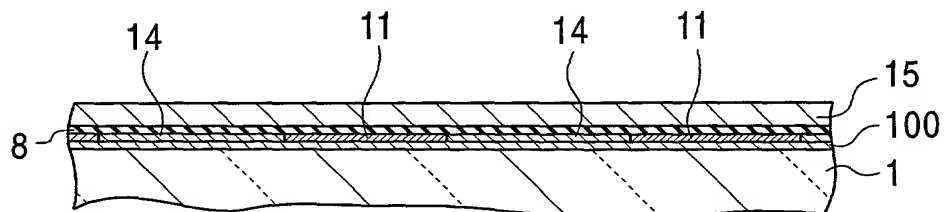


FIG. 1G

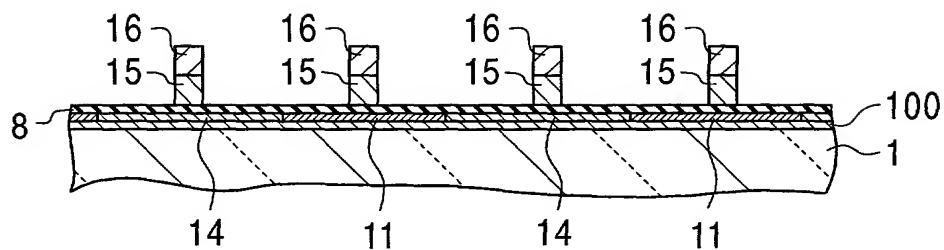


FIG. 1H

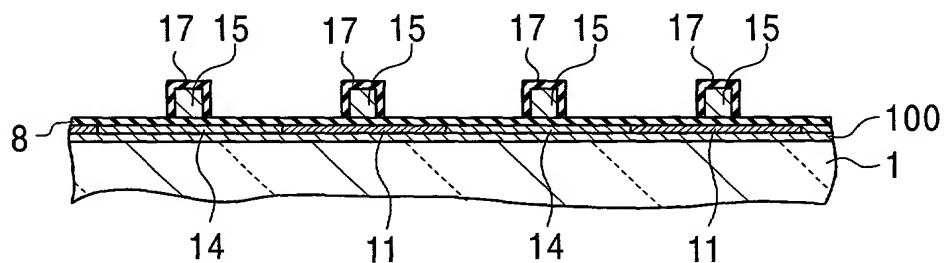


FIG. 1I

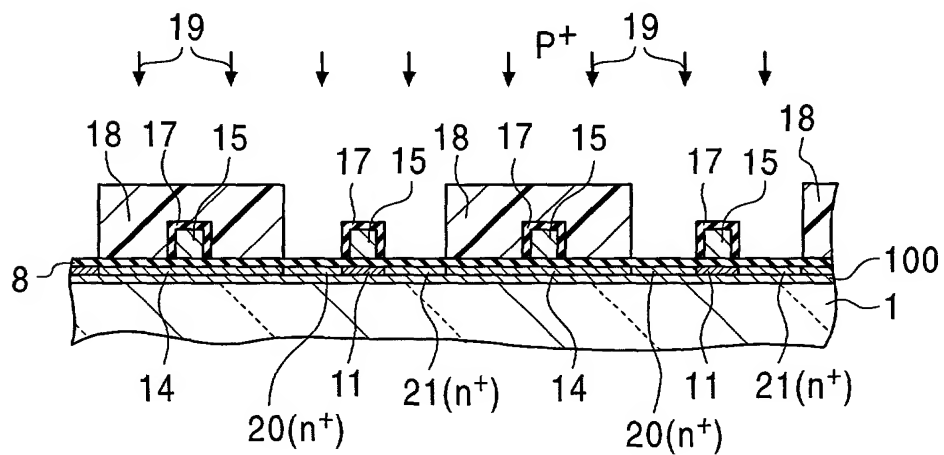


FIG. 1J

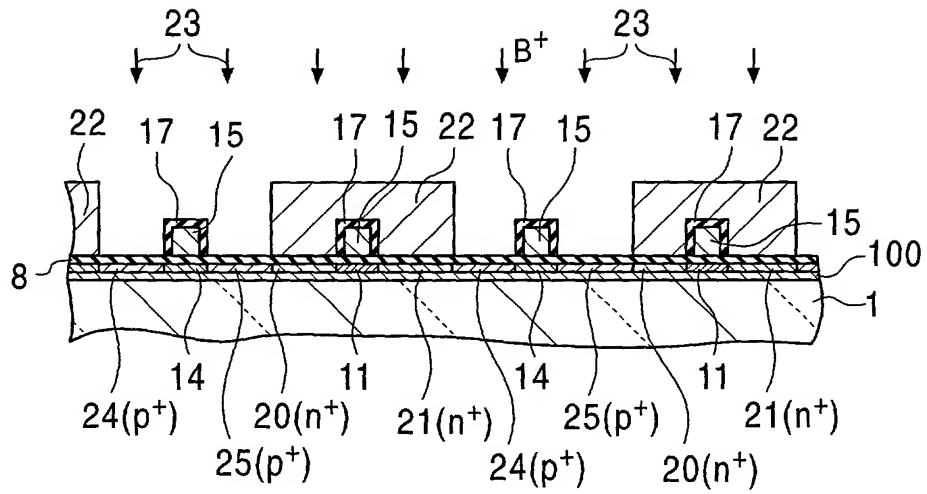


FIG. 1K

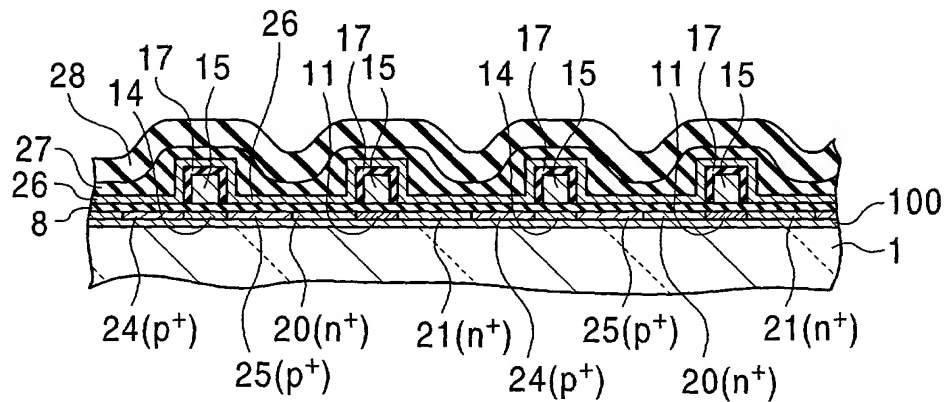


FIG. 1L

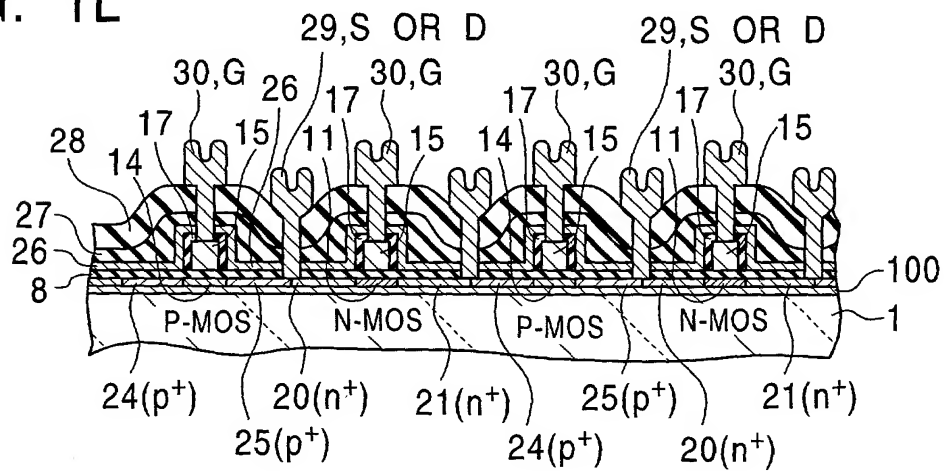
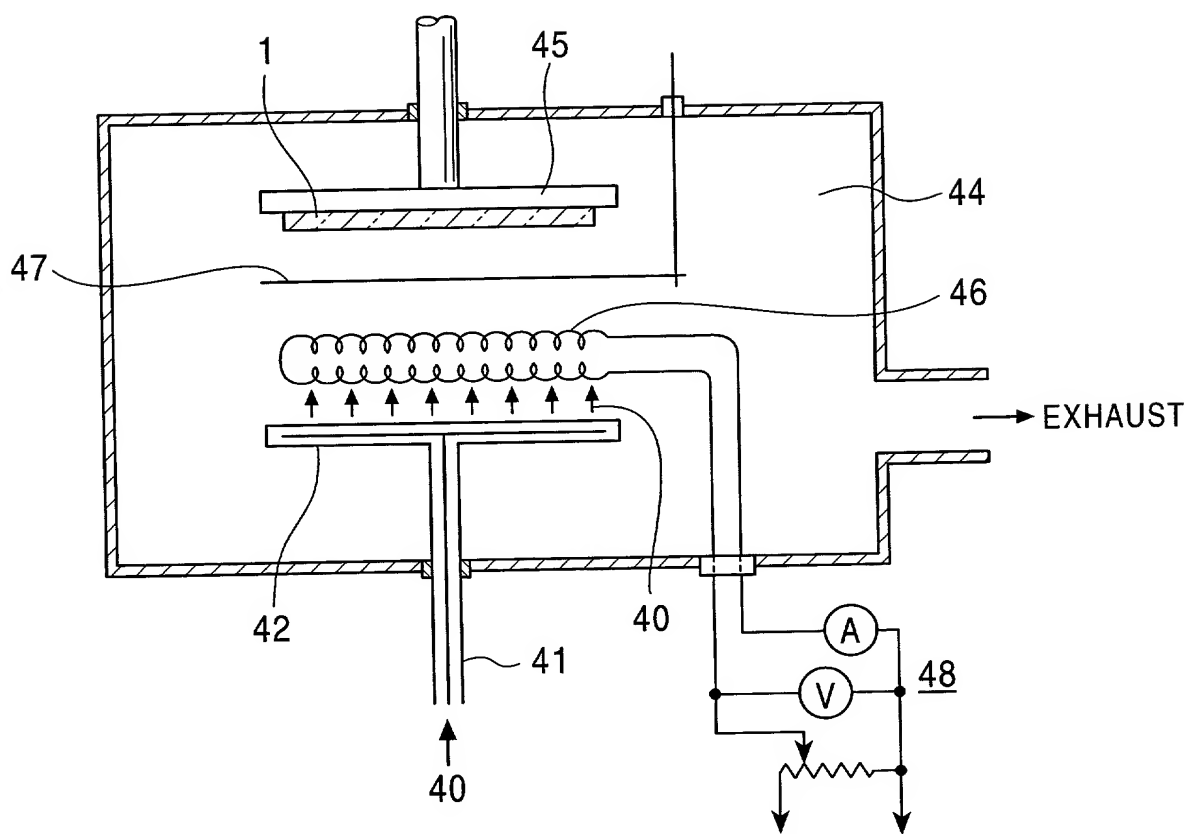


FIG. 2



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FIG. 3

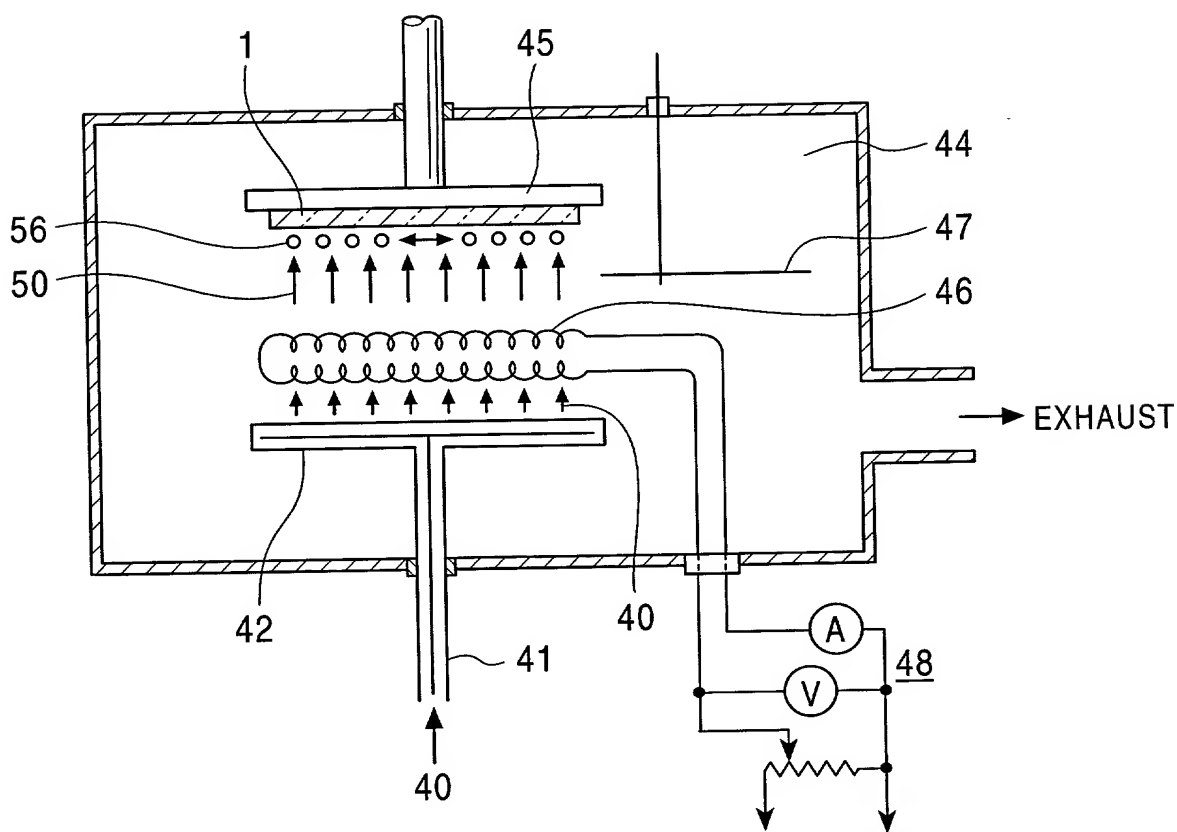


FIG. 4A

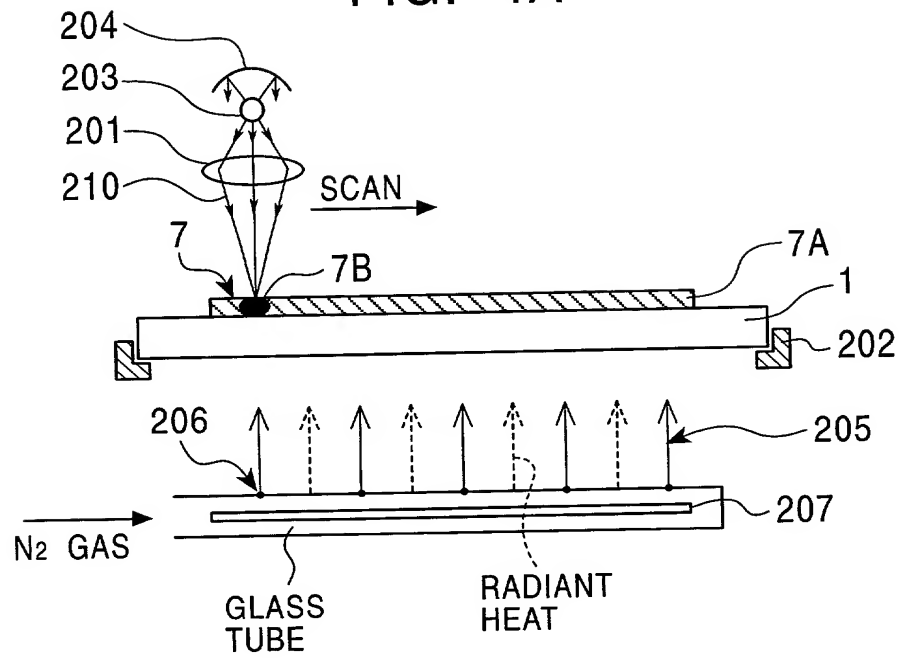


FIG. 4B

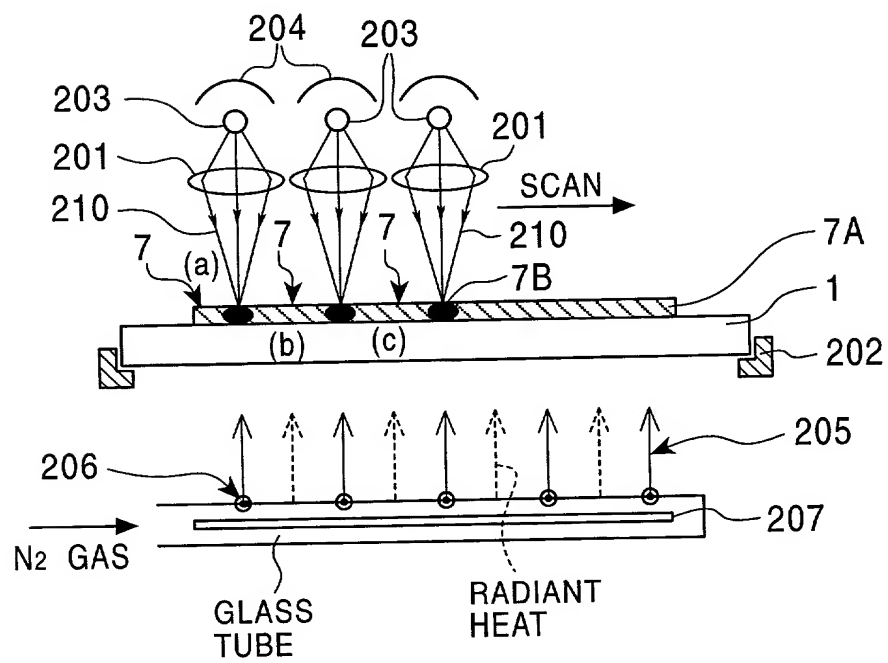


FIG. 4C

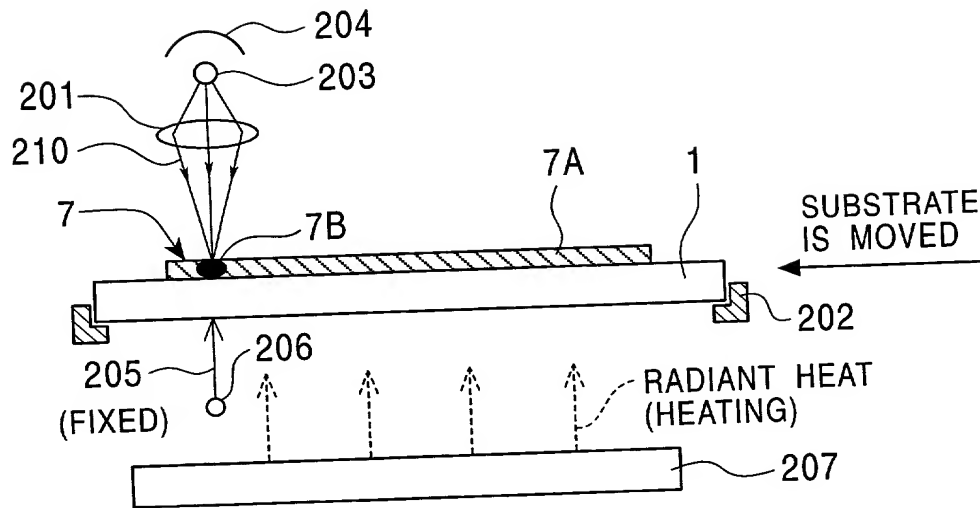


FIG. 4D

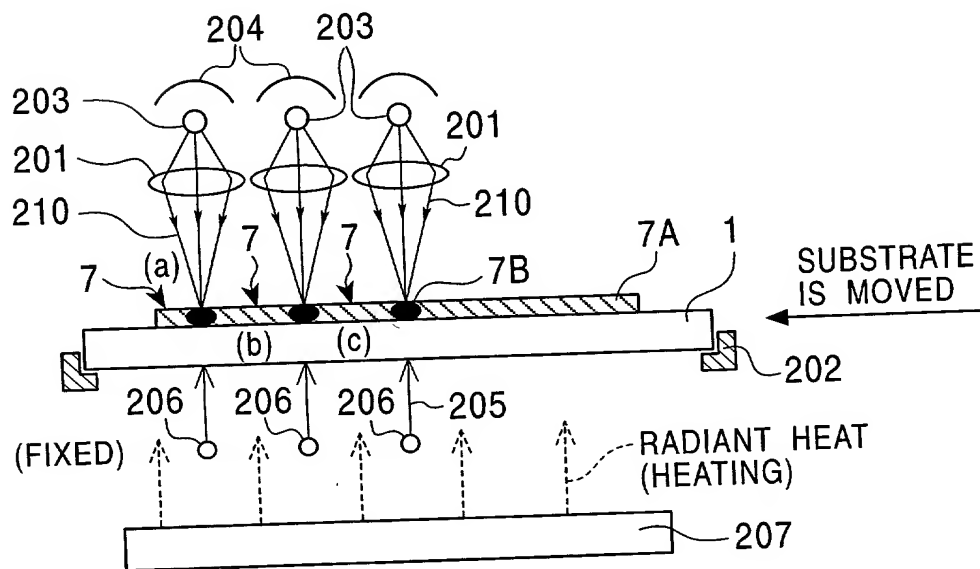
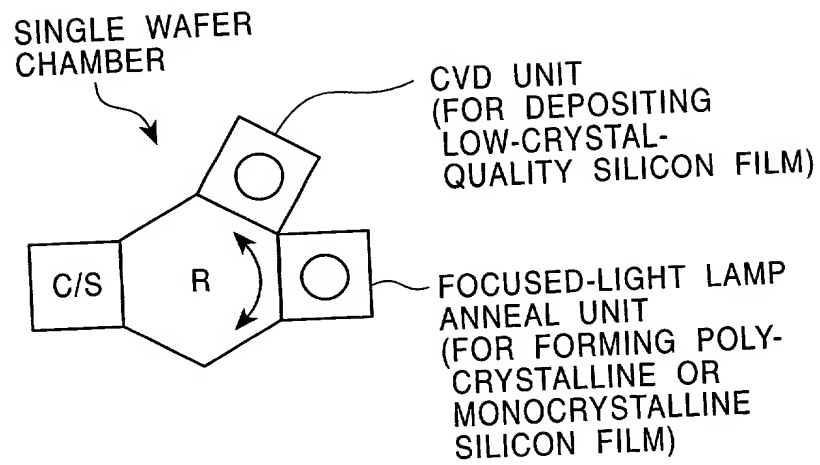


FIG. 5



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FIG. 6A

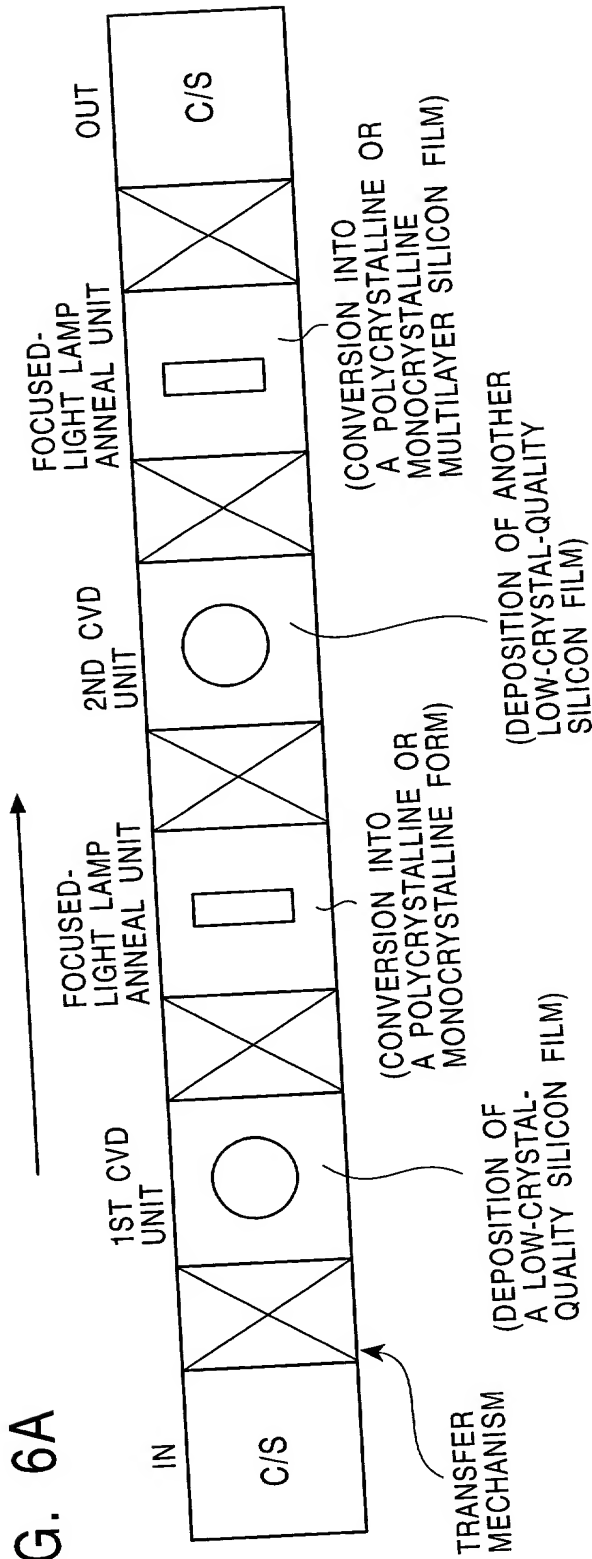


FIG. 6B

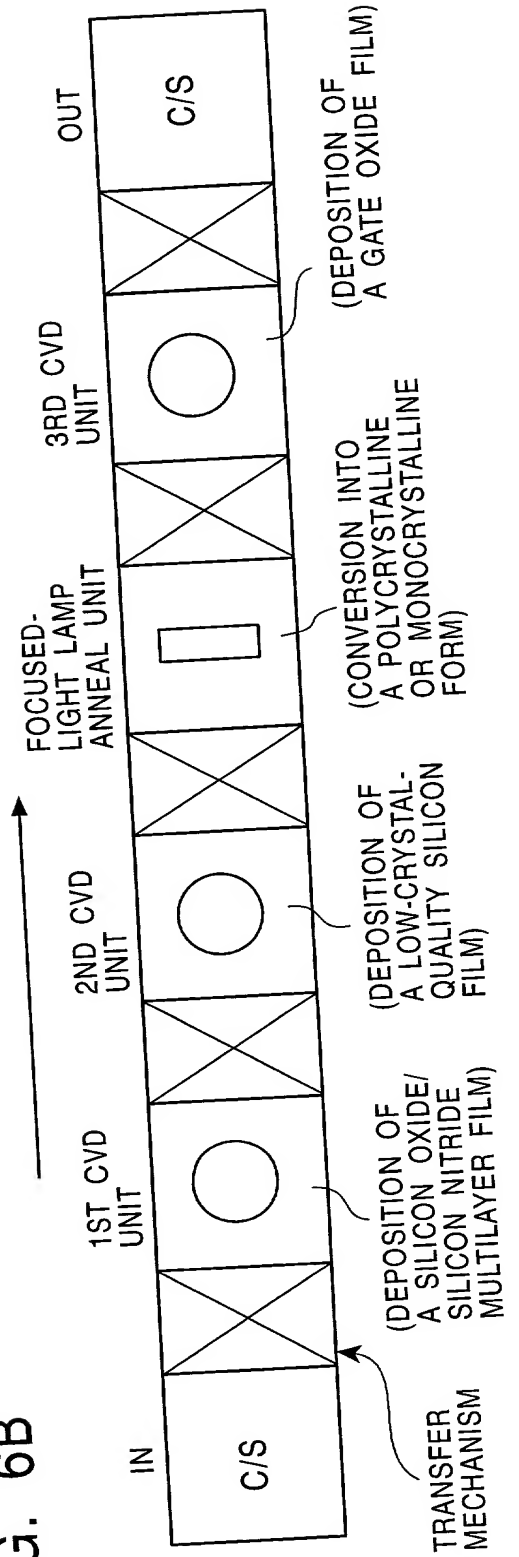


FIG. 7

1ST CVD UNIT (FOR DEPOSITION  
OF A SILICON OXIDE/SILICON  
NITRIDE MULTILAYER FILM)

2ND CVD UNIT  
(FOR DEPOSITION  
OF A LOW-CRYSTAL-  
QUALITY SILICON FILM)

ION DOPING UNIT OR  
ION IMPLANTATION UNIT  
(FOR DOPING A IV  
ELEMENT SUCH AS Sn,  
Ge, AND Pb)

3RD CVD UNIT  
(FOR DEPOSITION OF  
A SILICON OXIDE FILM OR  
A SILICON OXIDE/SILICON  
NITRIDE FILM)

FOCUSED-LIGHT LAMP  
ANNEAL UNIT

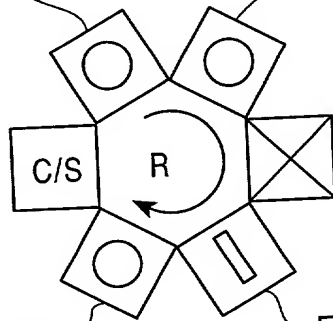


FIG. 8

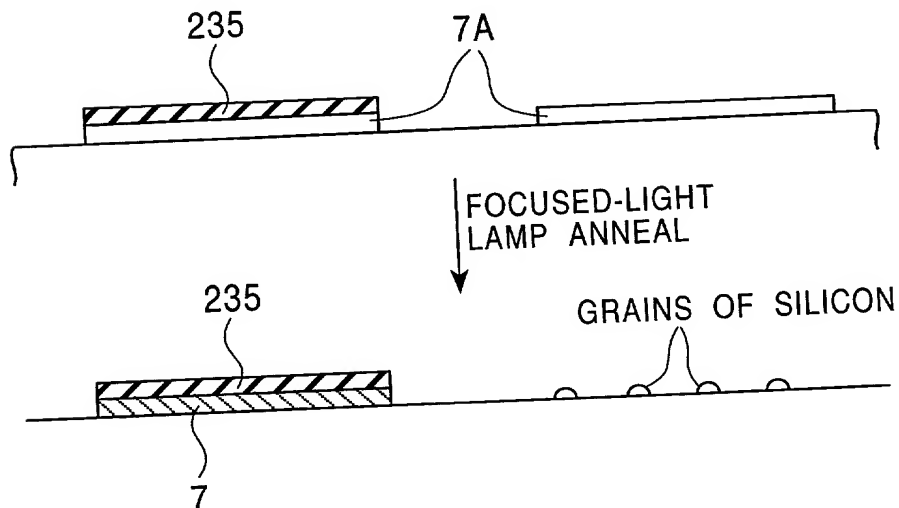


FIG. 9A

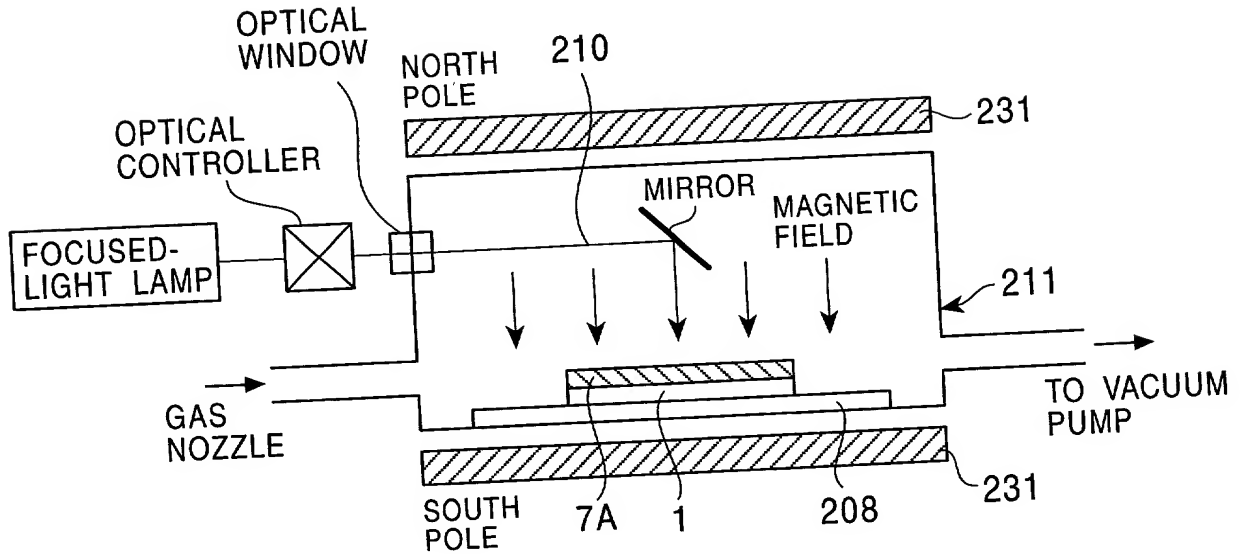


FIG. 9B

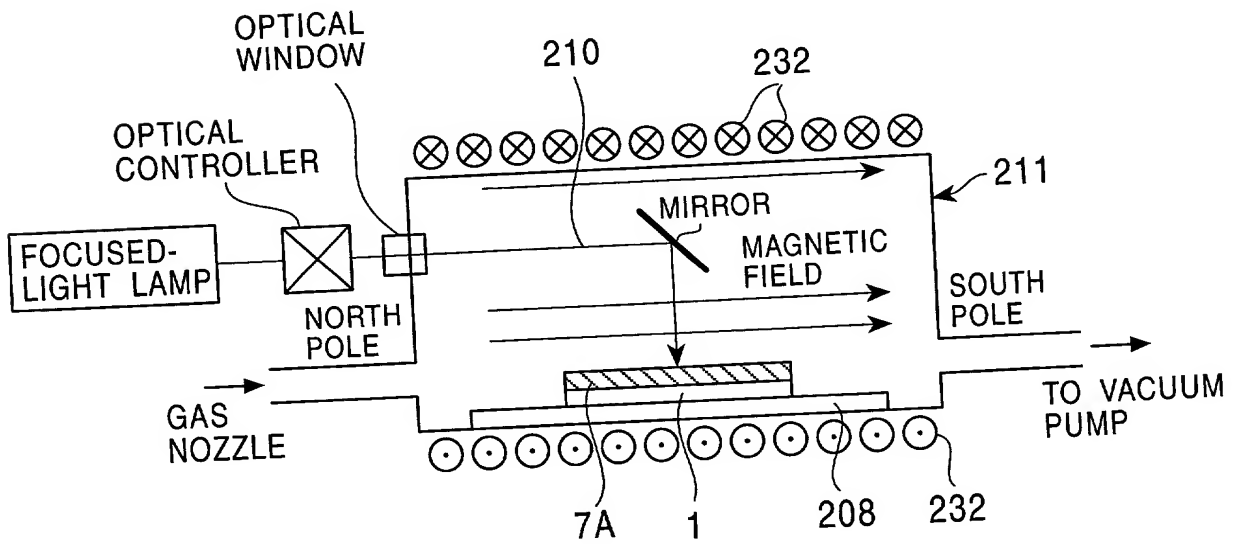


FIG. 9C

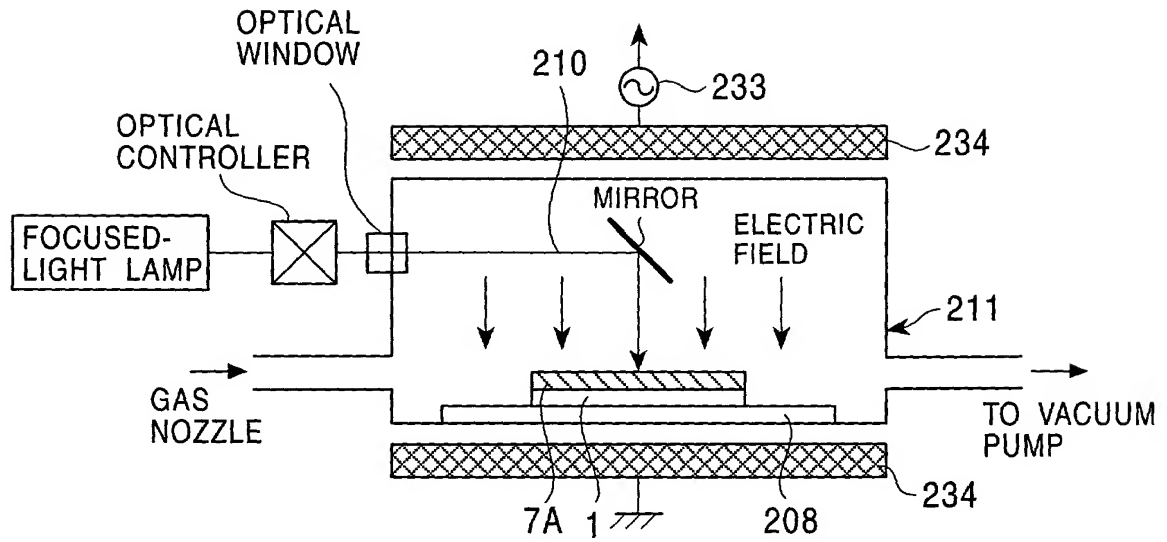


FIG. 9D

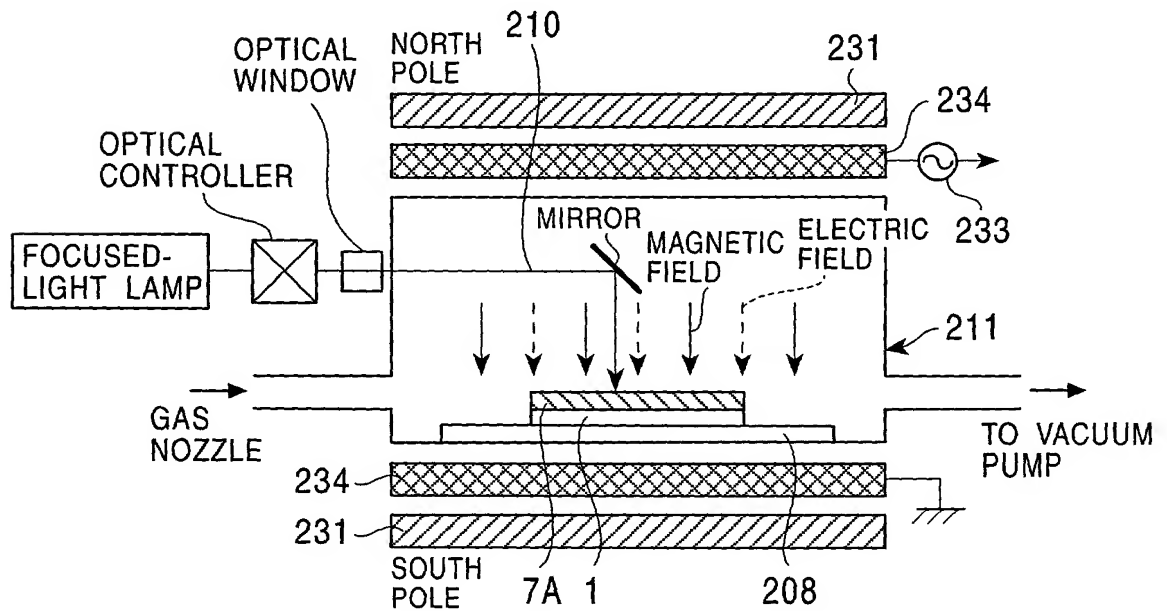


FIG. 10A

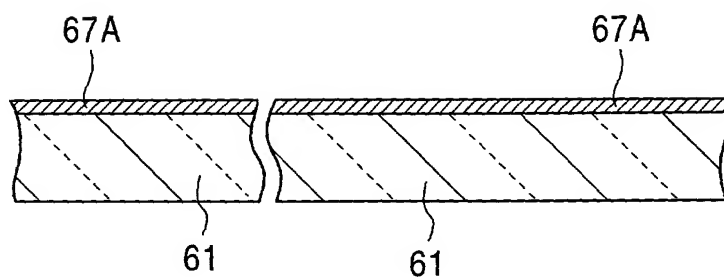


FIG. 10B

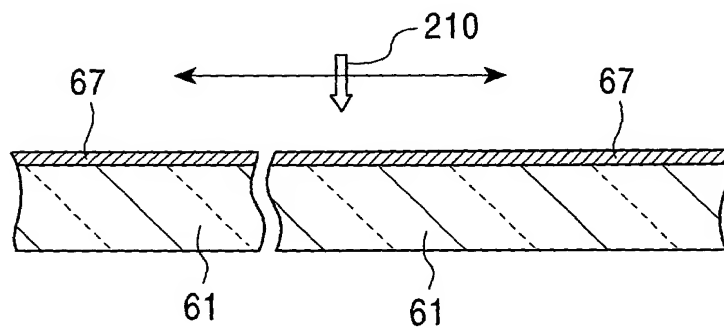


FIG. 10C

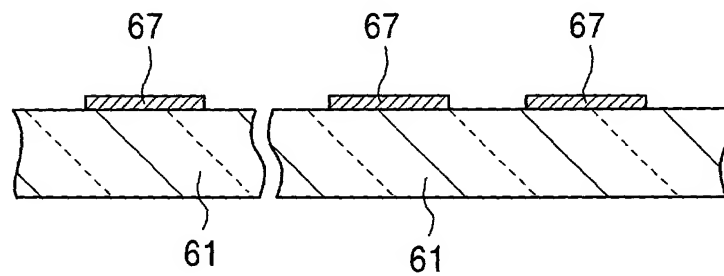


FIG. 10D

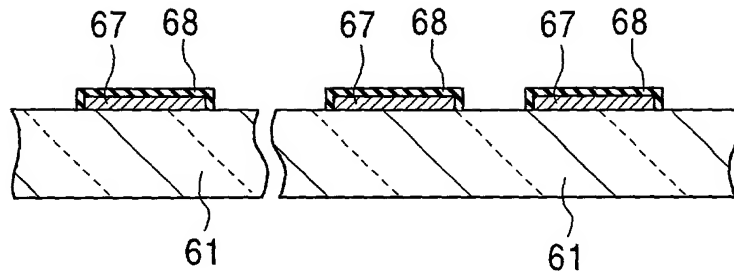


FIG. 10E

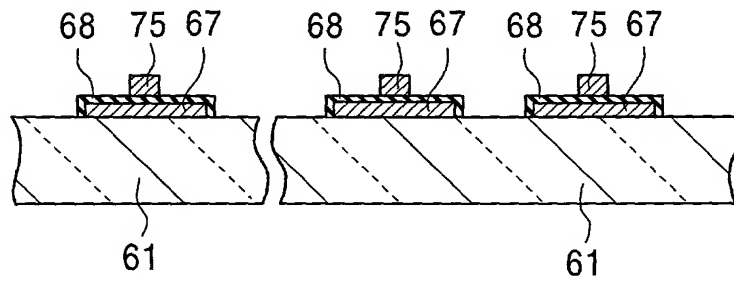


FIG. 10F

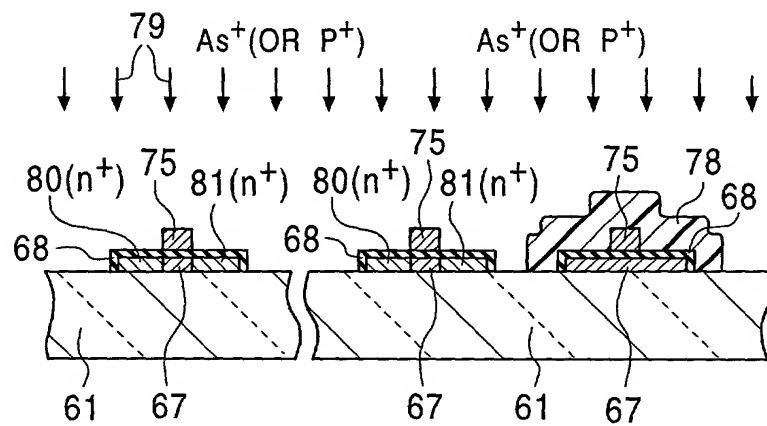


FIG. 10G

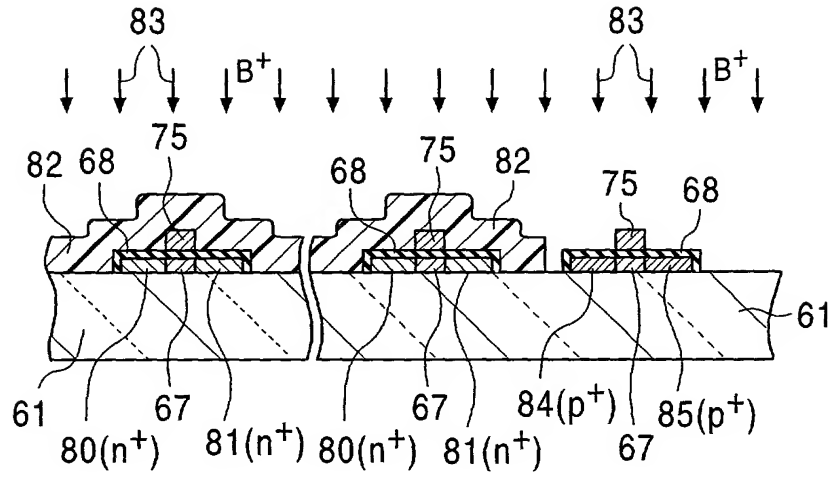


FIG. 10H

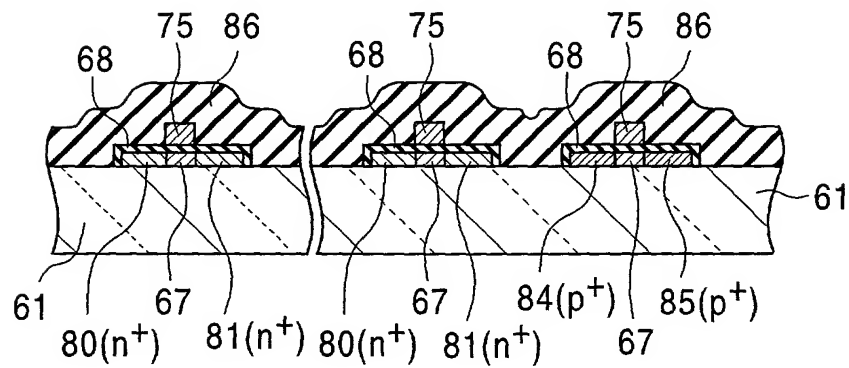


FIG. 10I

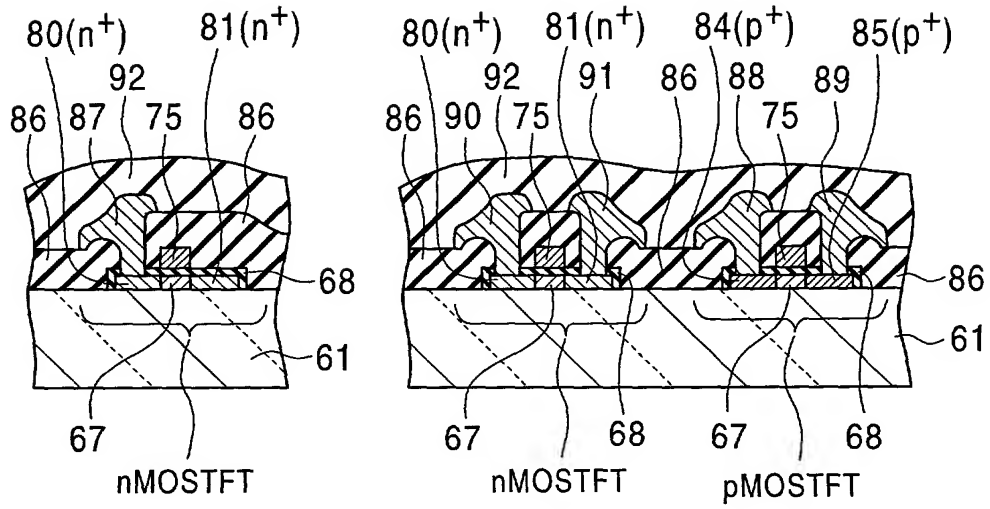


FIG. 10J

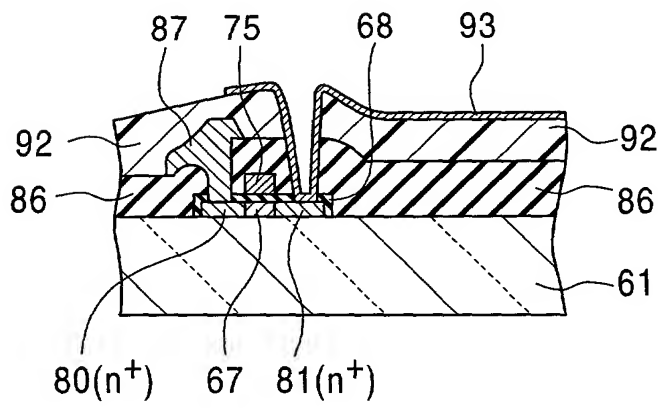




FIG. 10K

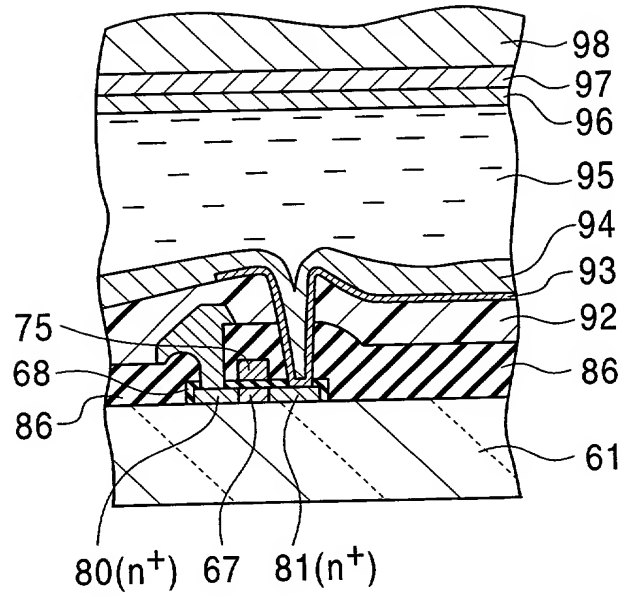


FIG. 10L

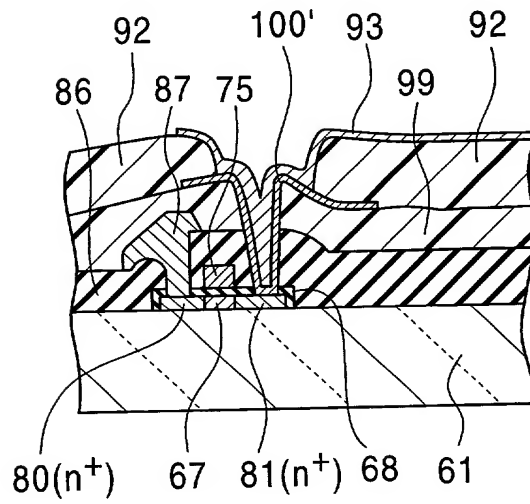
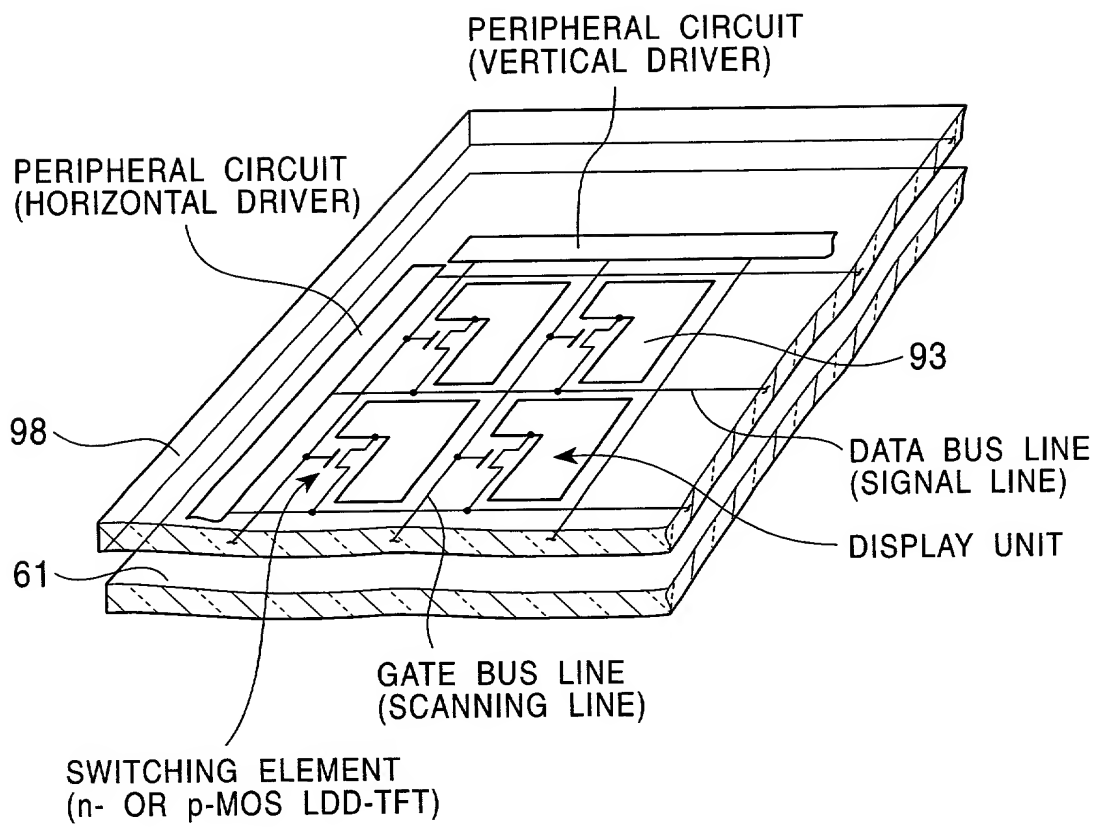


FIG. 11



10075774.024402

FIG. 12

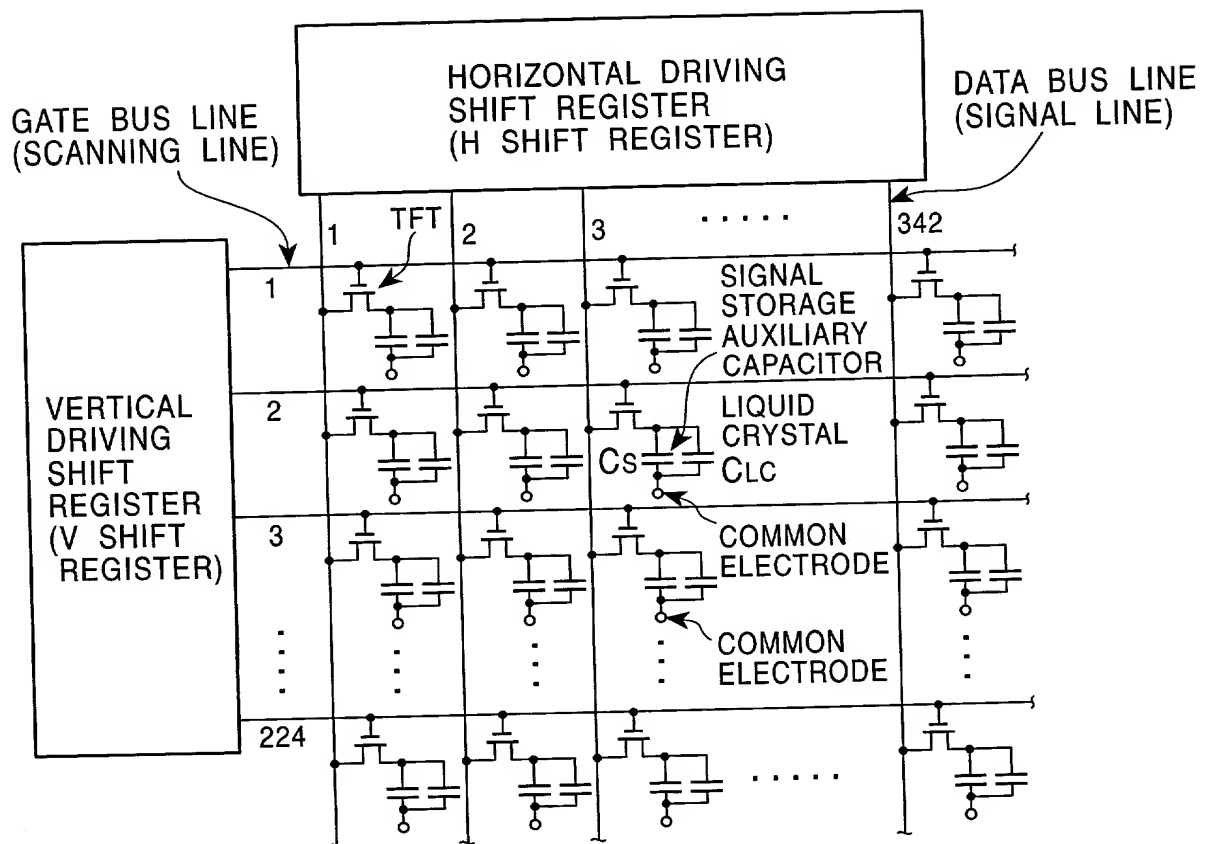


FIG. 13A

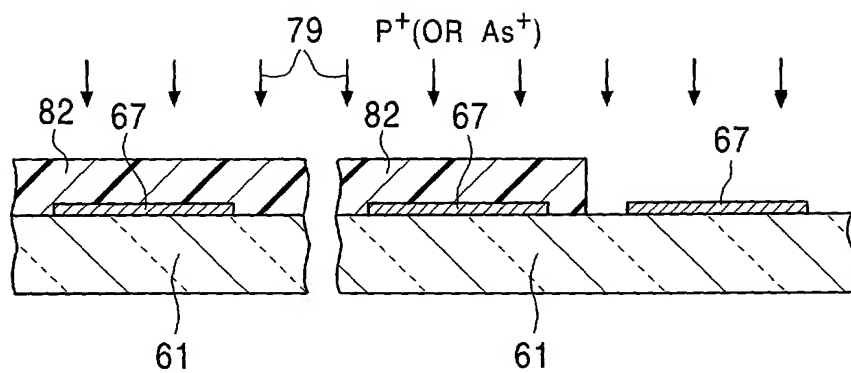


FIG. 13B

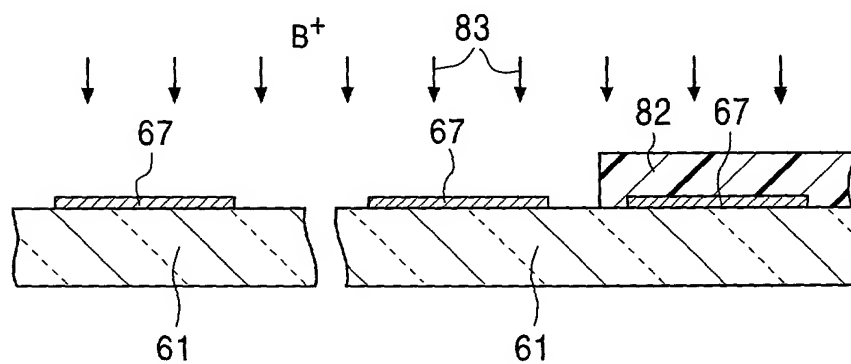


FIG. 13C

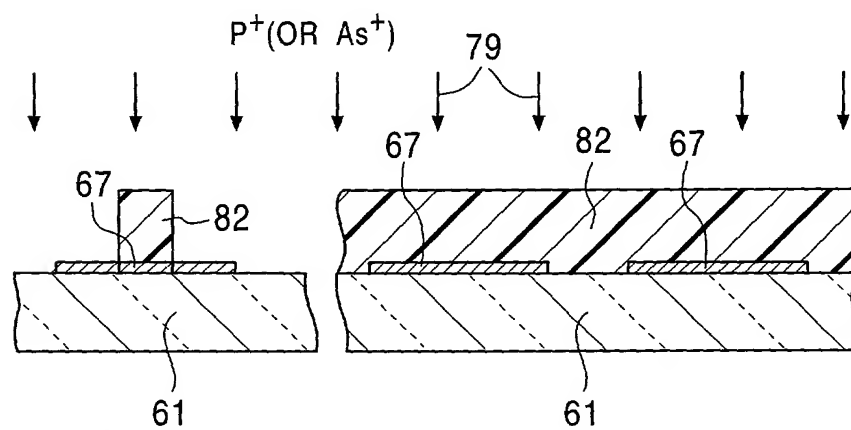


FIG. 13D

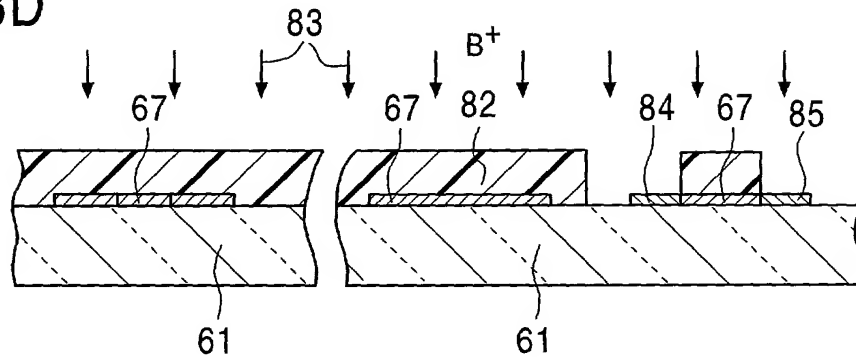


FIG. 13E

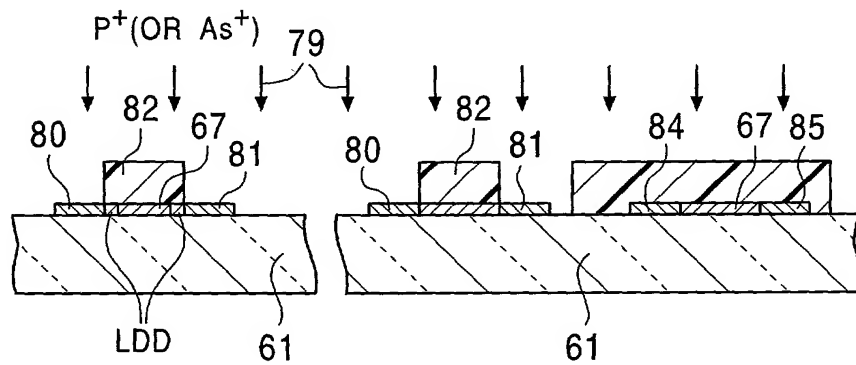


FIG. 13F

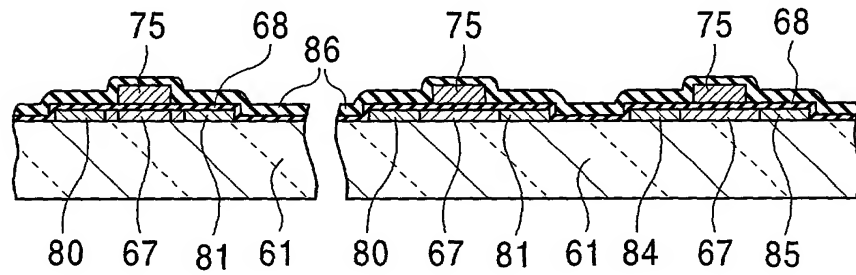


FIG. 13G

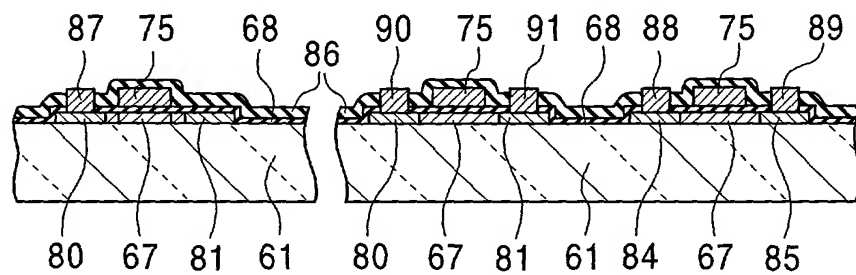


FIG. 14A

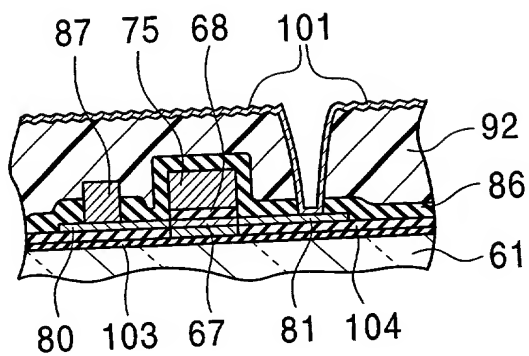


FIG. 14B

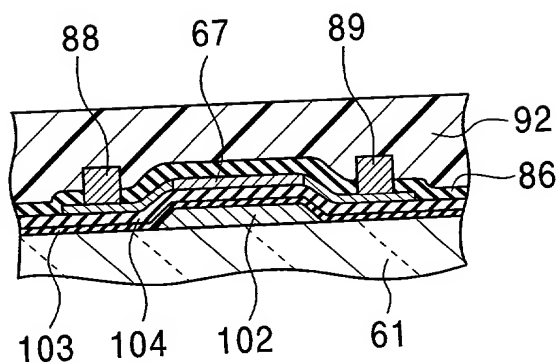
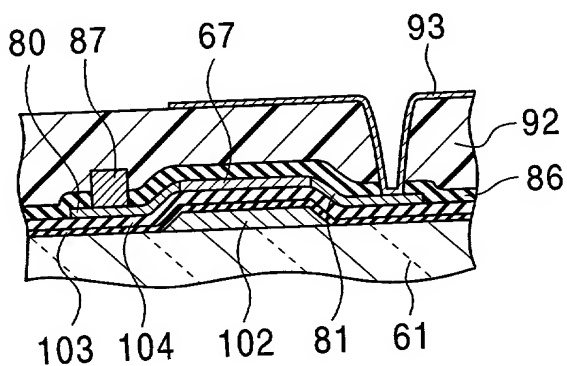


FIG. 14C

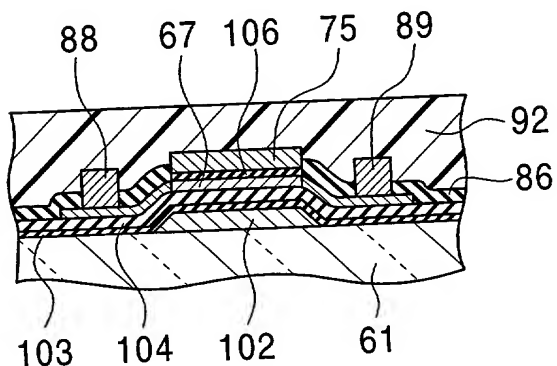
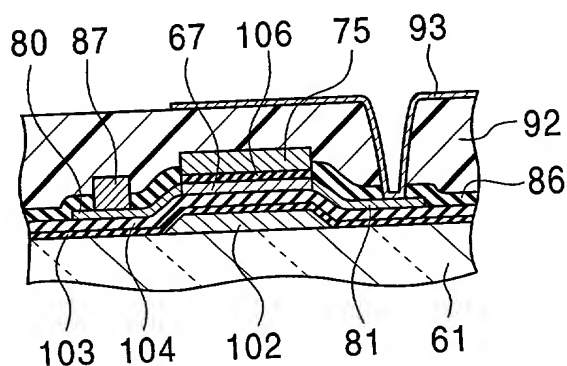


FIG. 15A

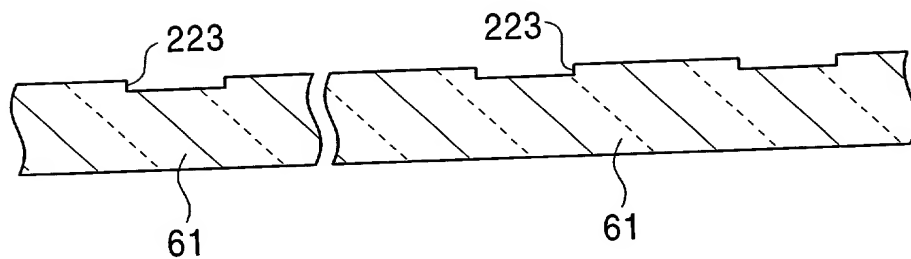


FIG. 15B

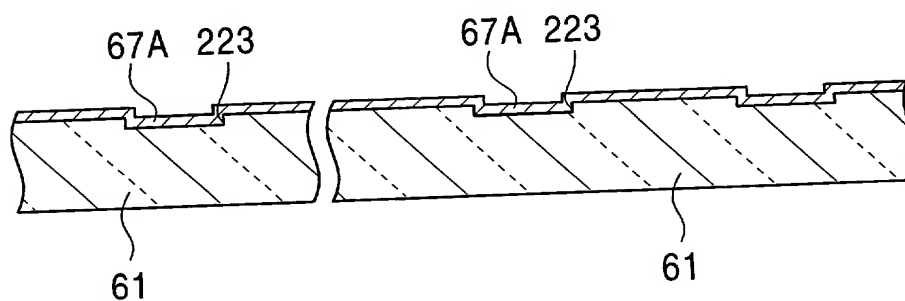
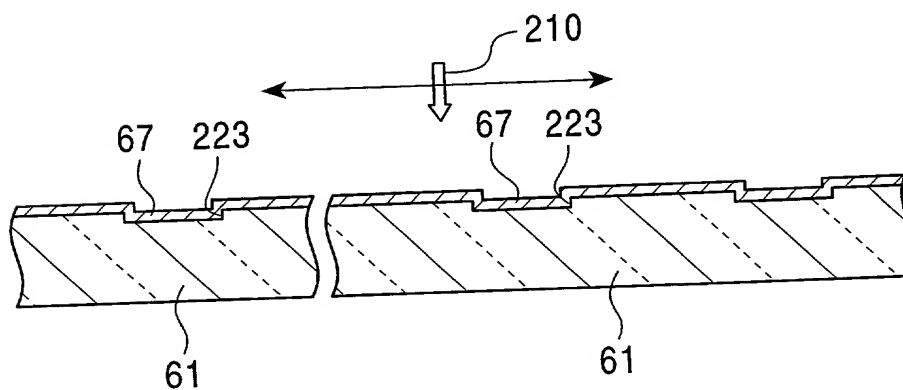


FIG. 15C



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FIG. 16A

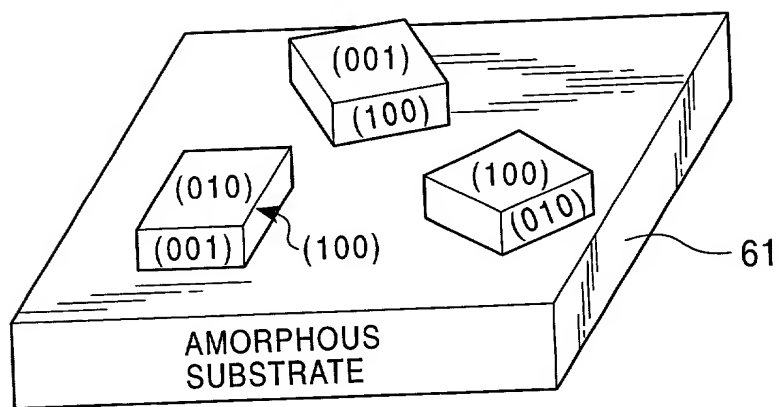


FIG. 16B

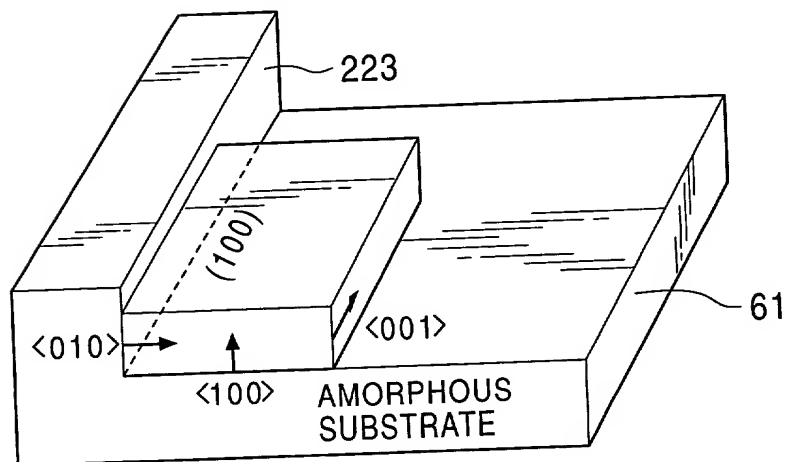




FIG. 17A

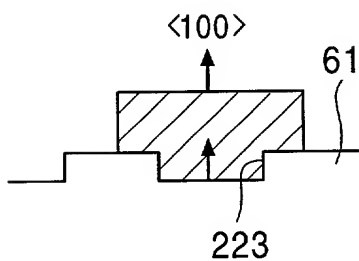


FIG. 17B

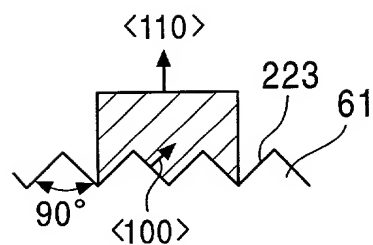


FIG. 17C

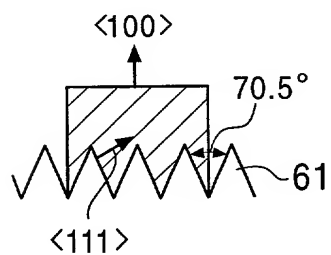


FIG. 17D

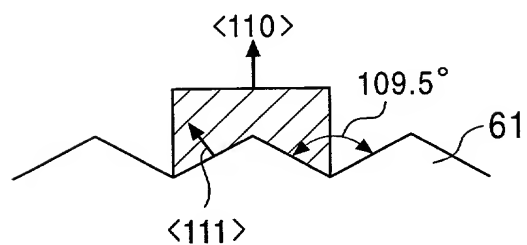


FIG. 17E

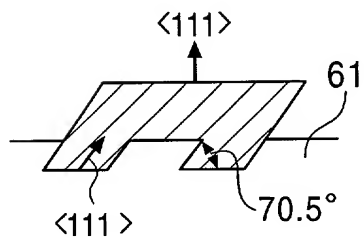
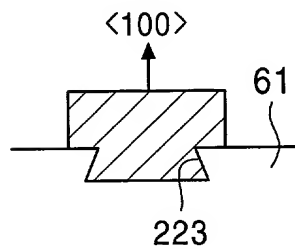


FIG. 17F



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FIG. 18A

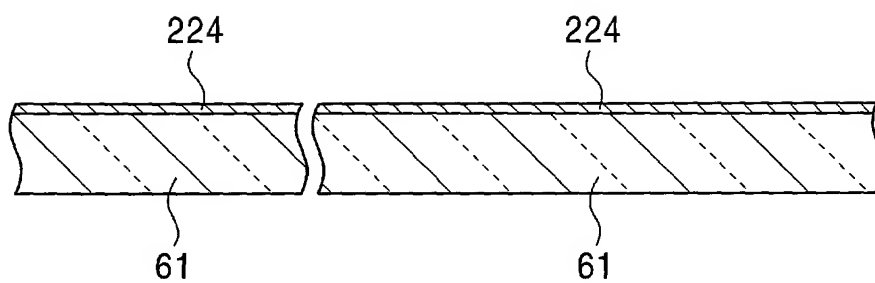


FIG. 18B

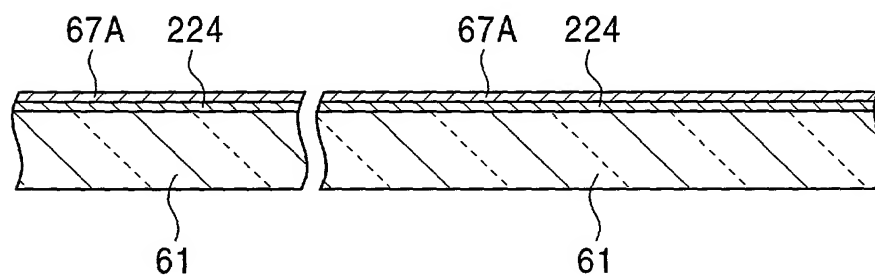


FIG. 18C

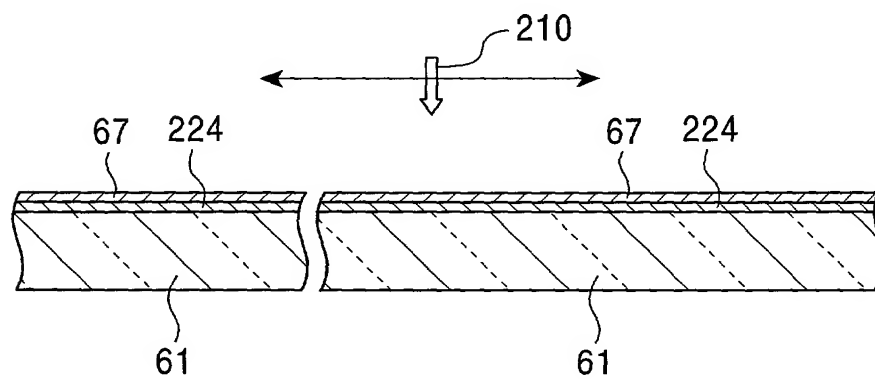


FIG. 19A

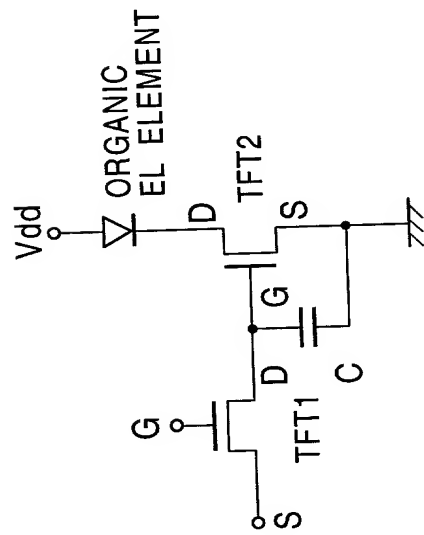


FIG. 19C

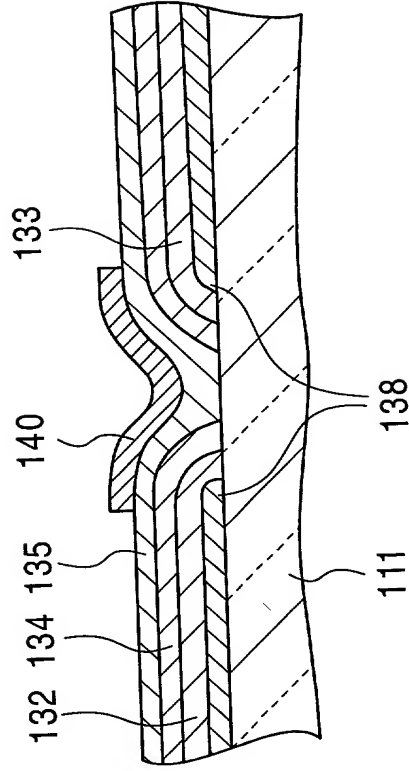


FIG. 19B

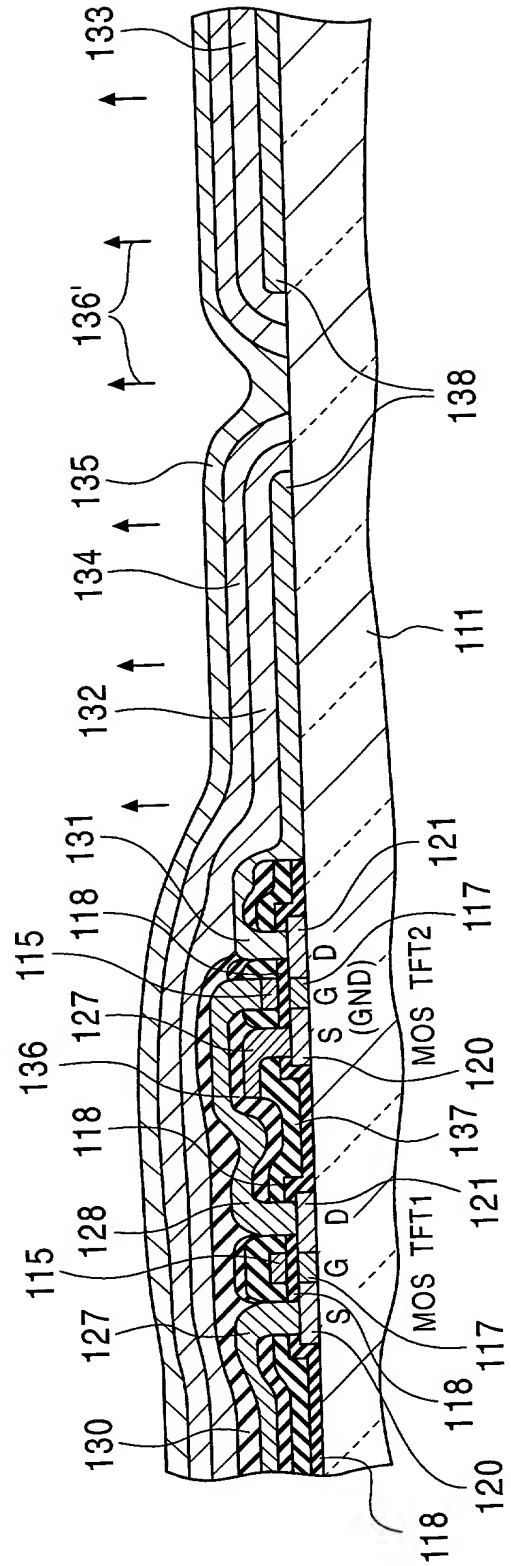


FIG. 20A

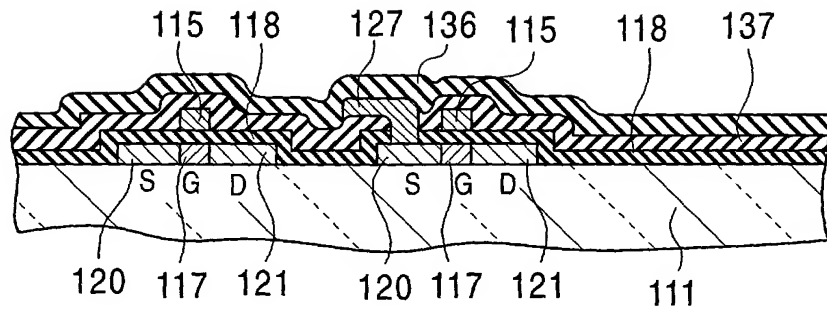


FIG. 20B

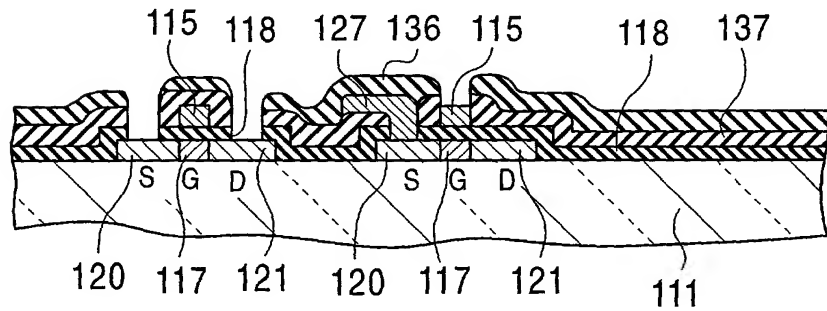


FIG. 20C

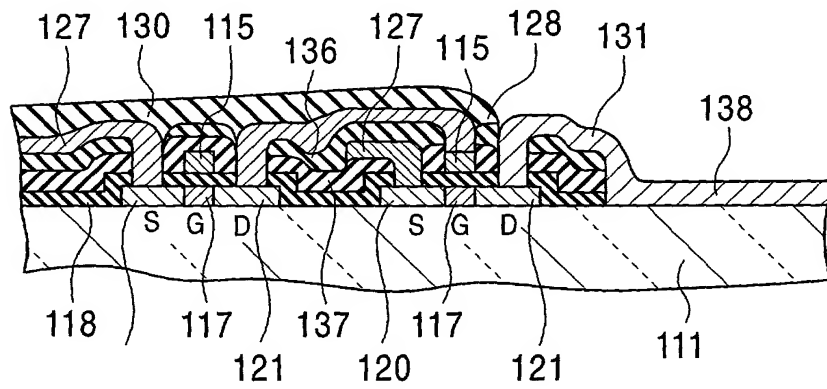
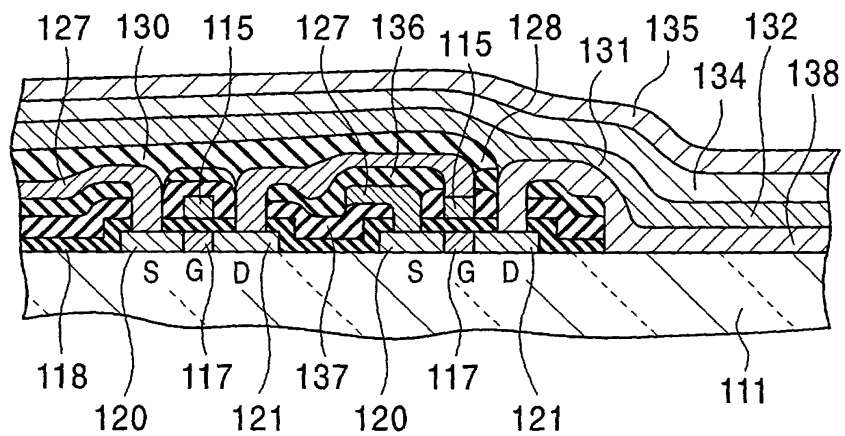


FIG. 20D



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FIG. 21A

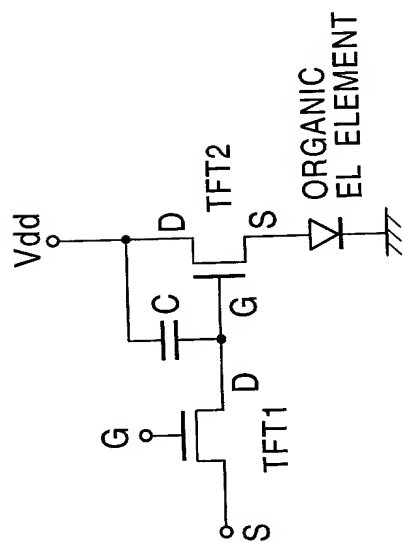


FIG. 21C

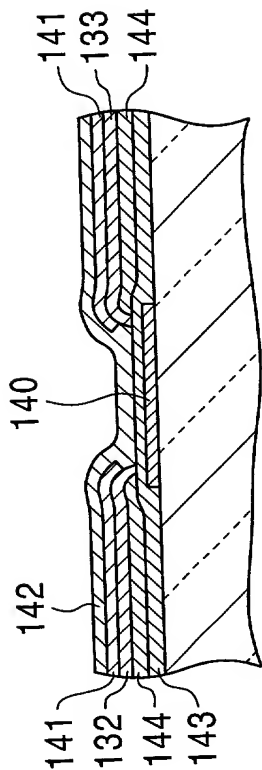


FIG. 21B

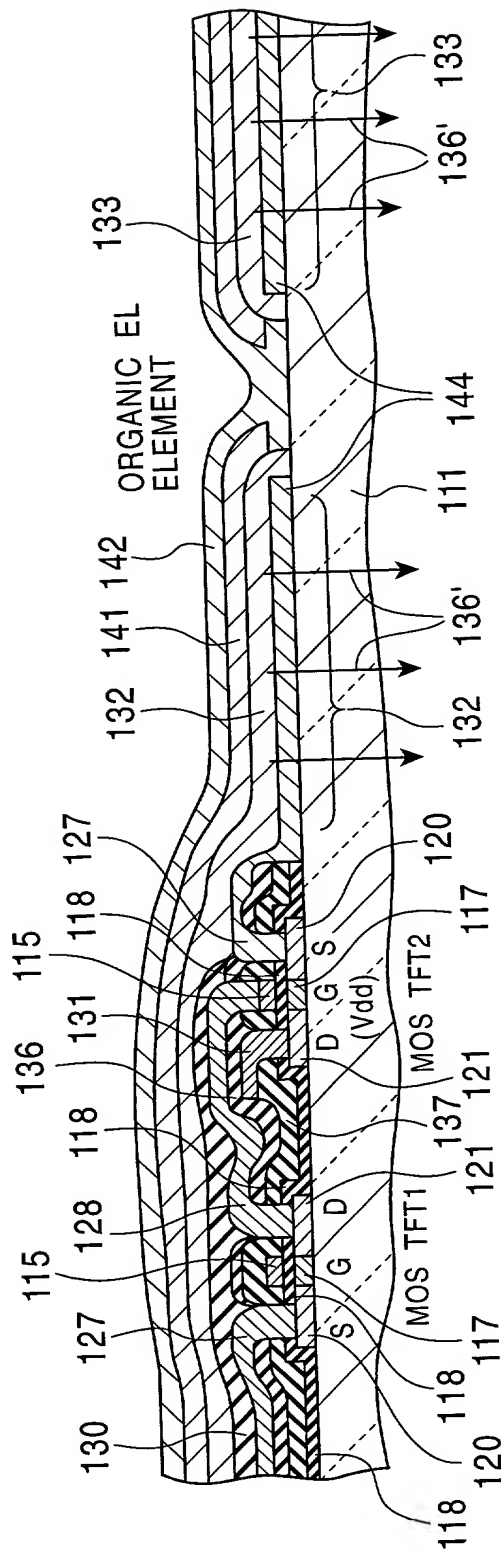


FIG. 22A

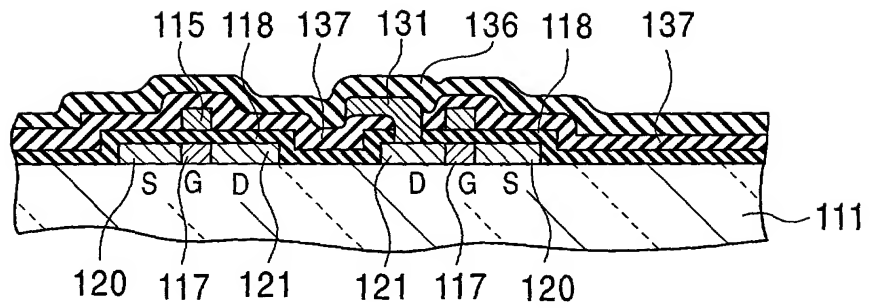


FIG. 22B

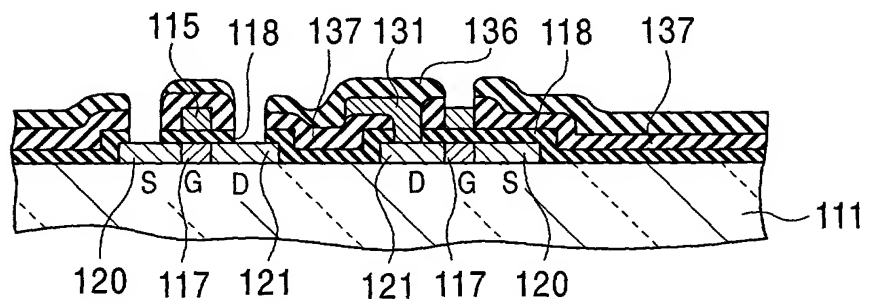


FIG. 22C

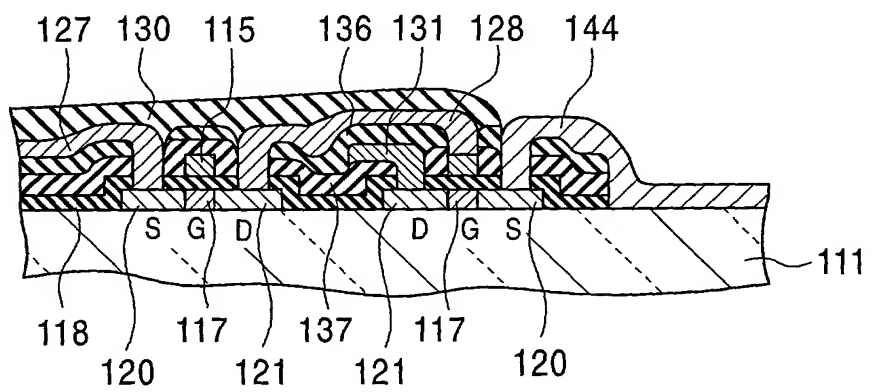
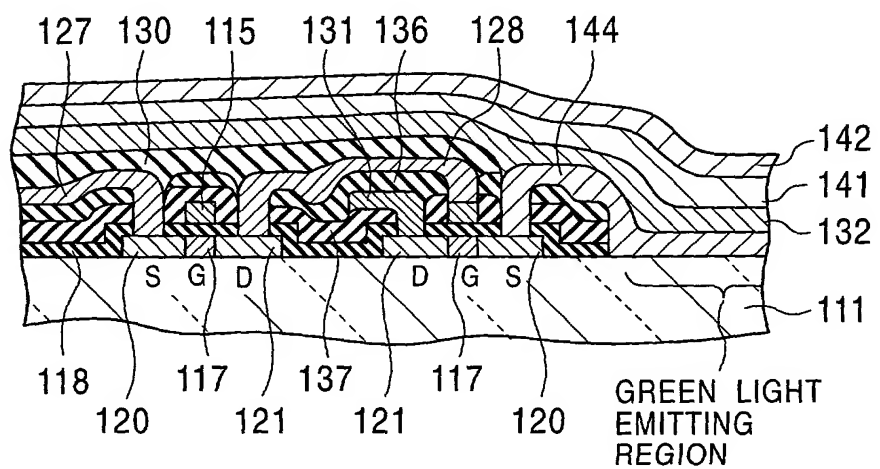


FIG. 22D



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FIG. 23A

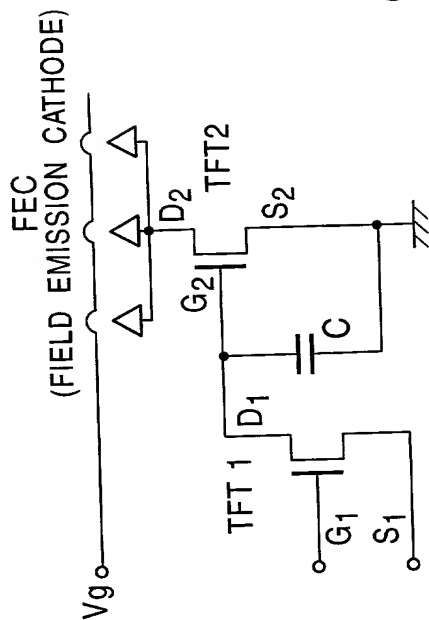


FIG. 23C

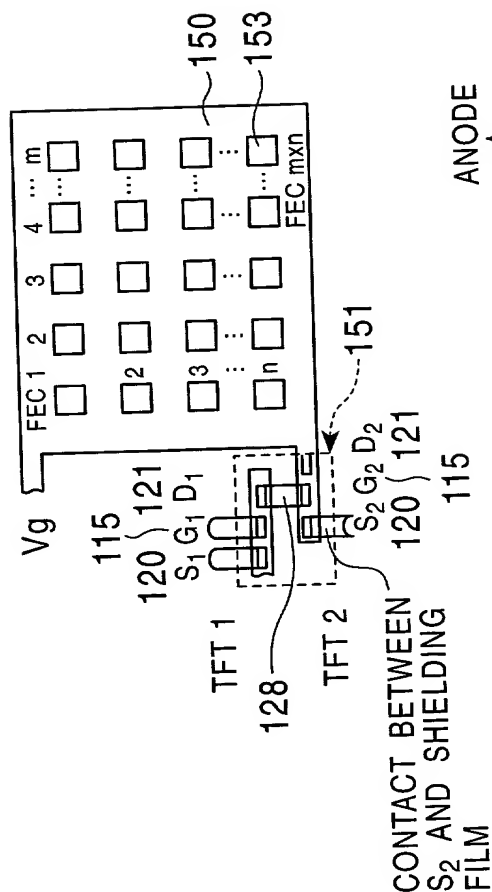


FIG. 23B

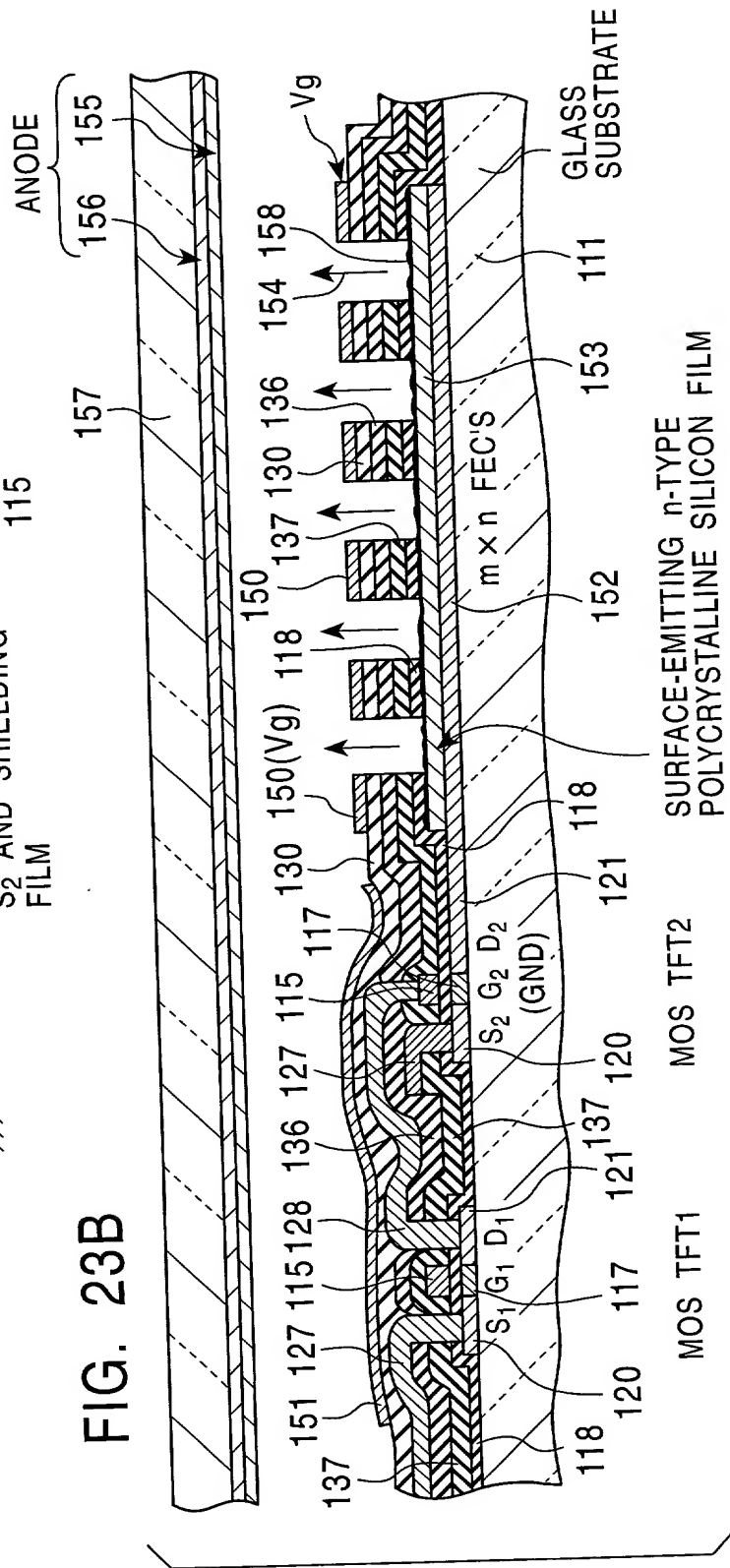


FIG. 24A

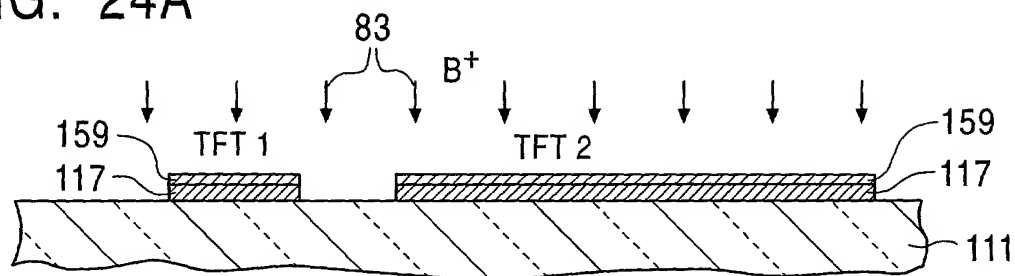


FIG. 24B

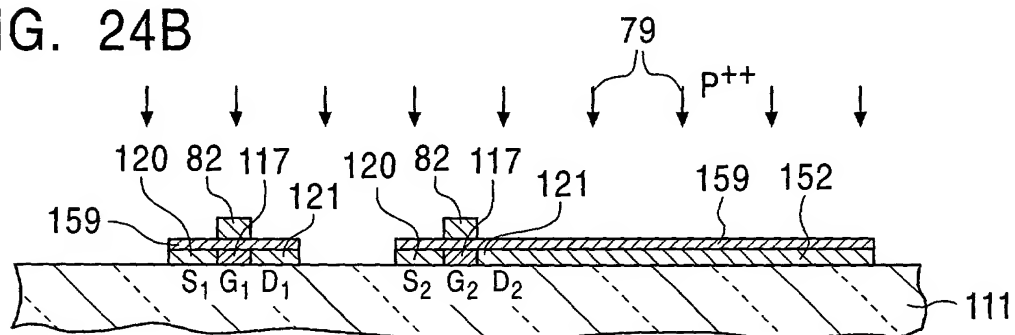


FIG. 24C

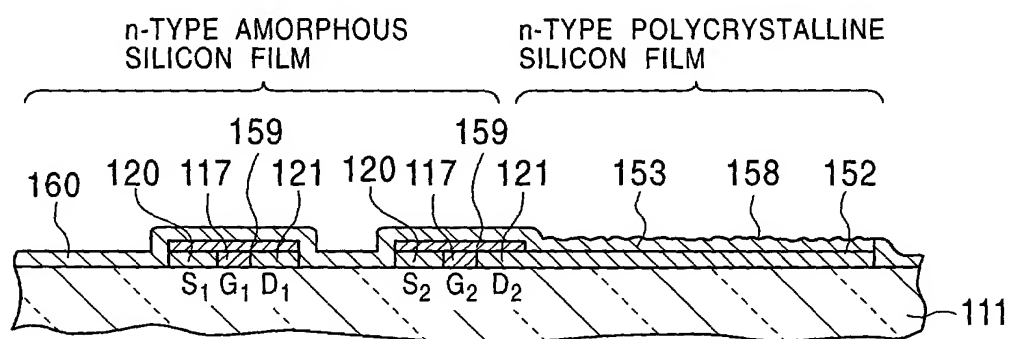


FIG. 24D

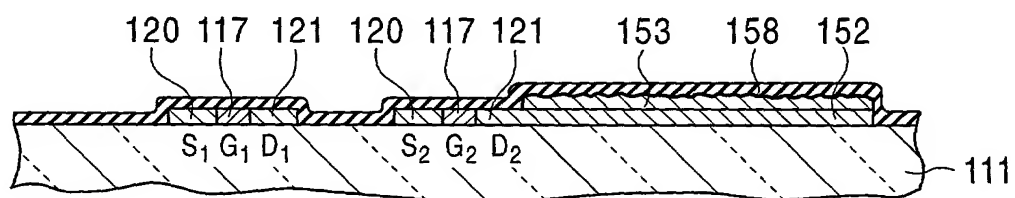




FIG. 24E

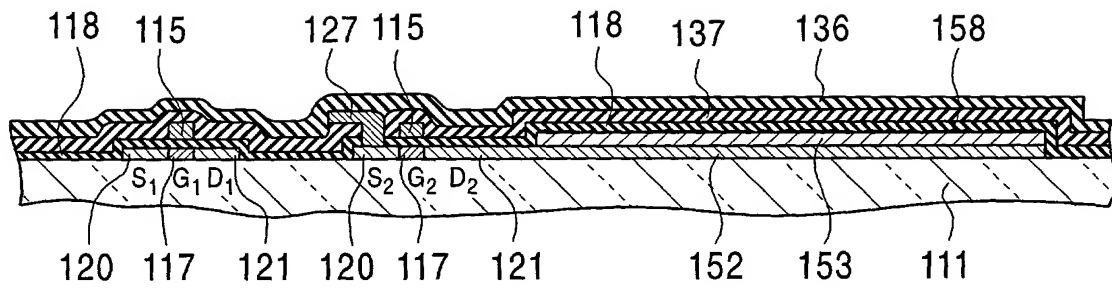


FIG. 24F

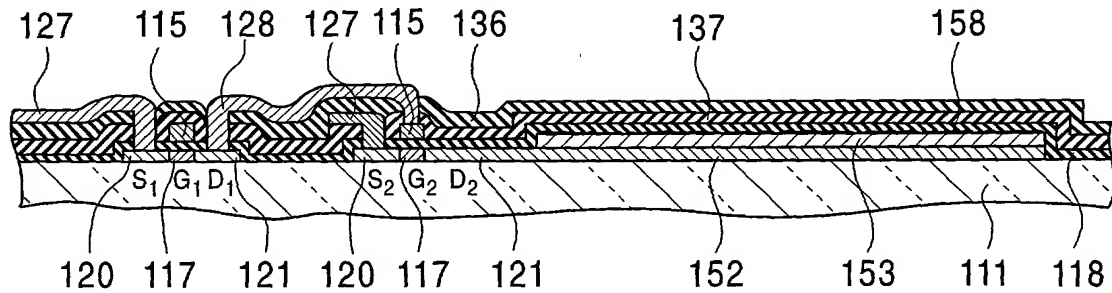


FIG. 24G

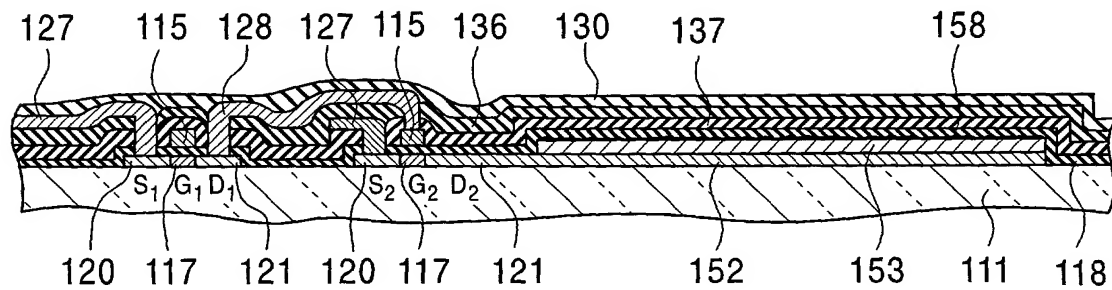
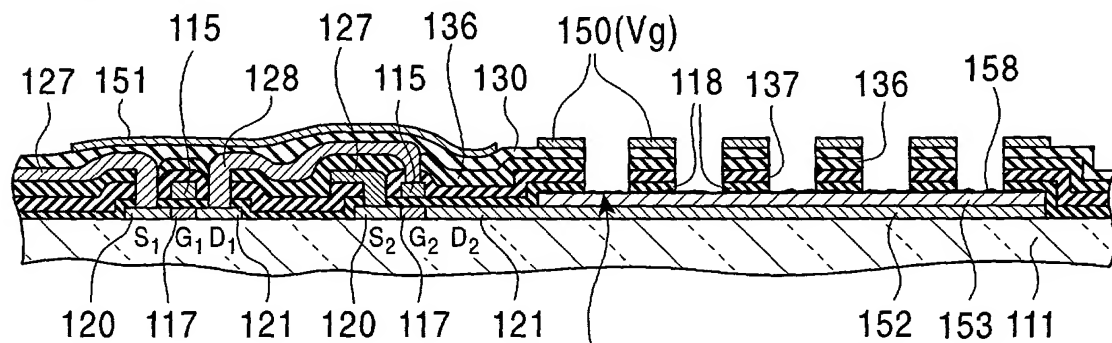


FIG. 24H



SURFACE-EMITTING FEC  
FORMED OF AN n-TYPE  
POLYCRYSTALLINE SILICON FILM

FIG. 25A

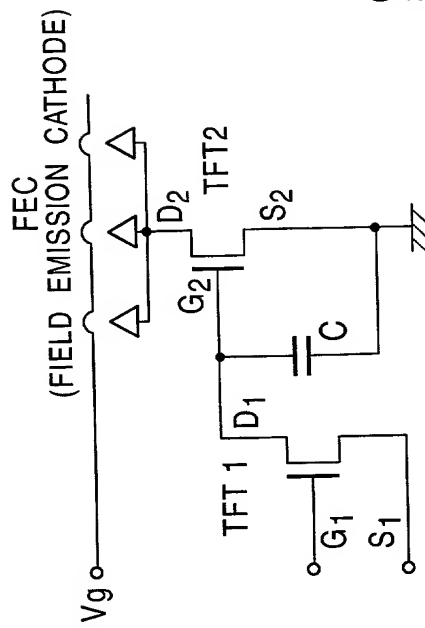


FIG. 25C

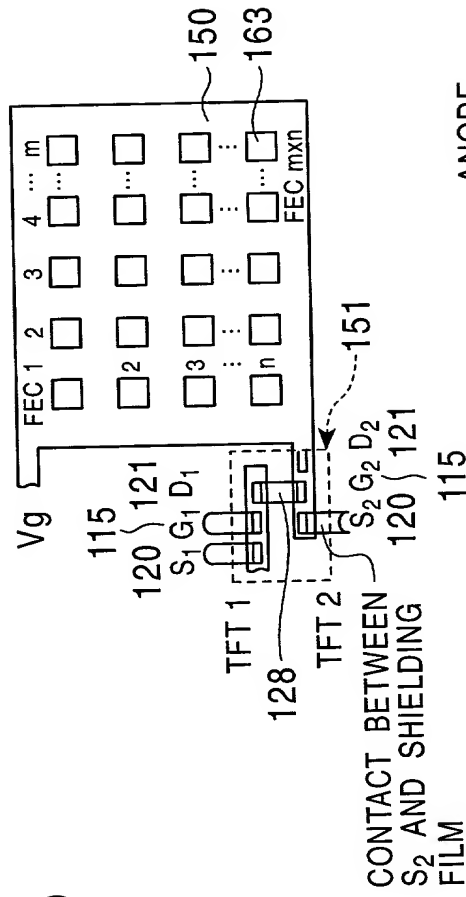


FIG. 25B

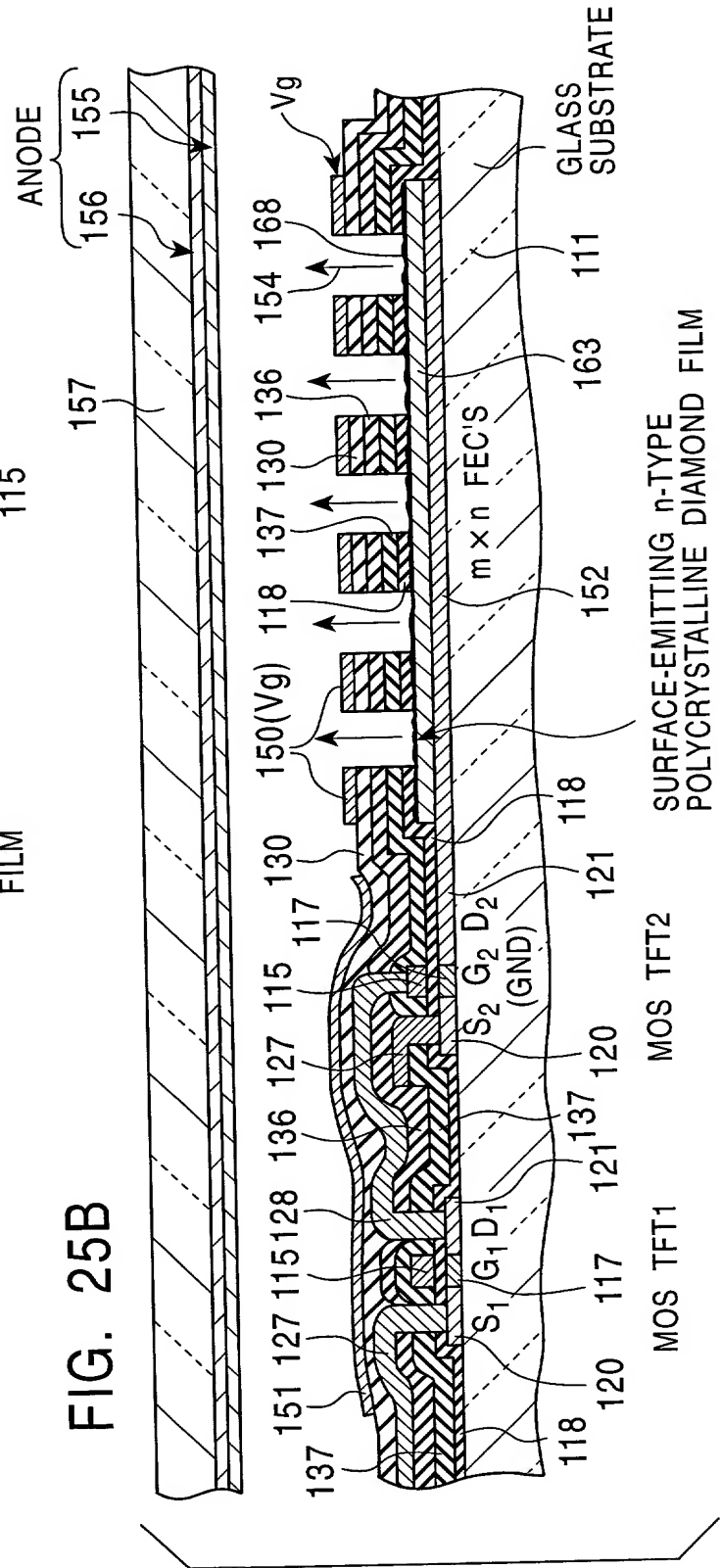


FIG. 26A

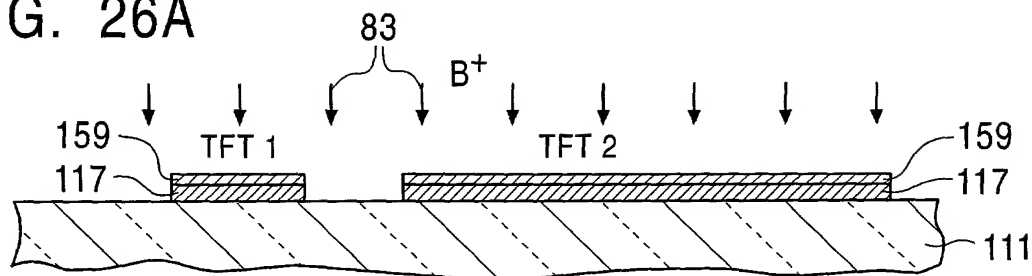


FIG. 26B

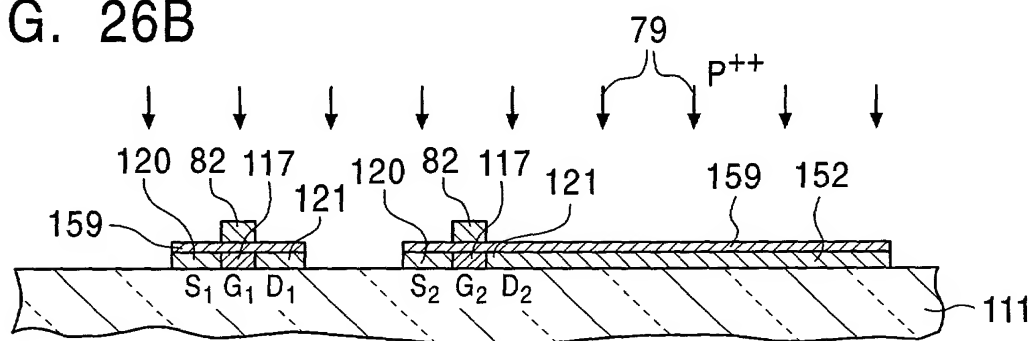


FIG. 26C

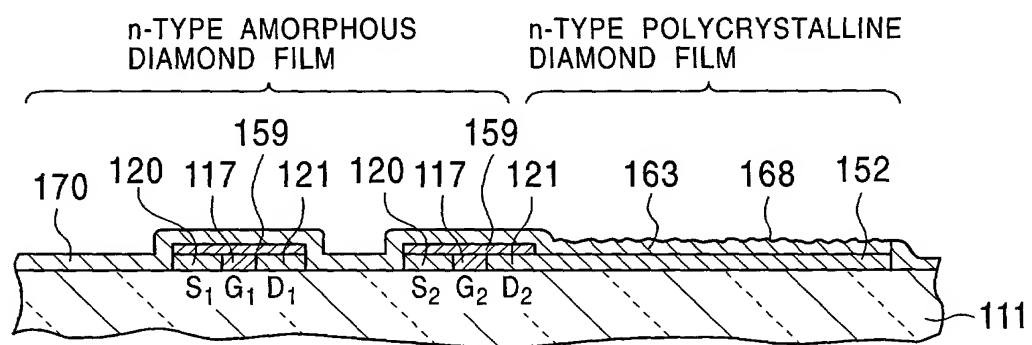


FIG. 26D

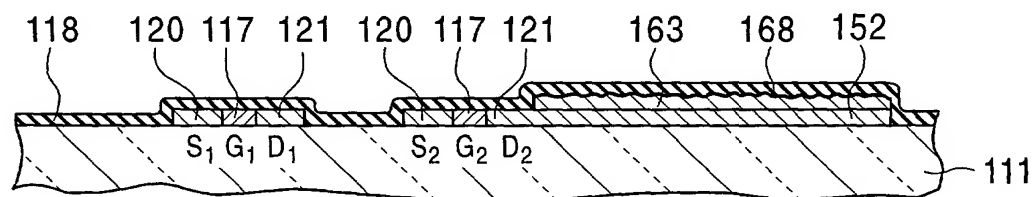


FIG. 26E

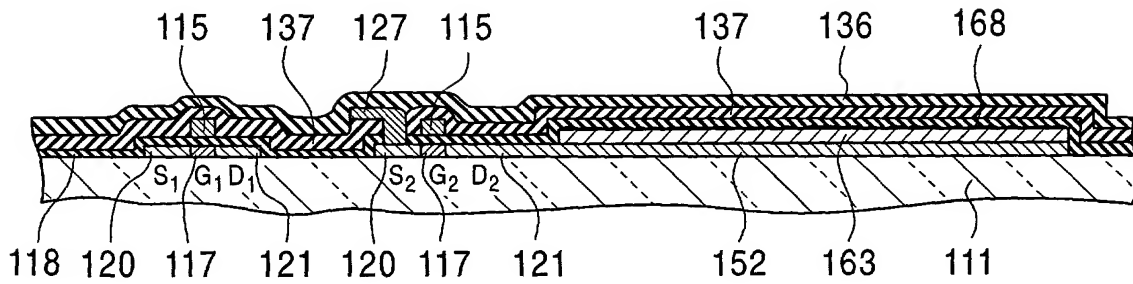


FIG. 26F

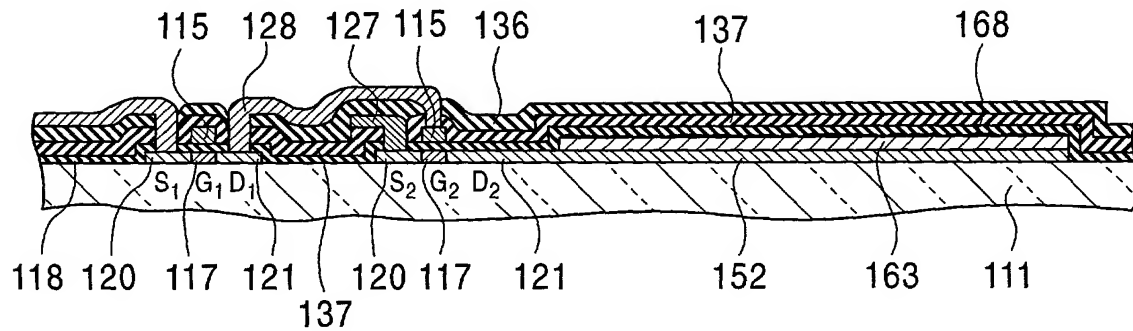


FIG. 26G

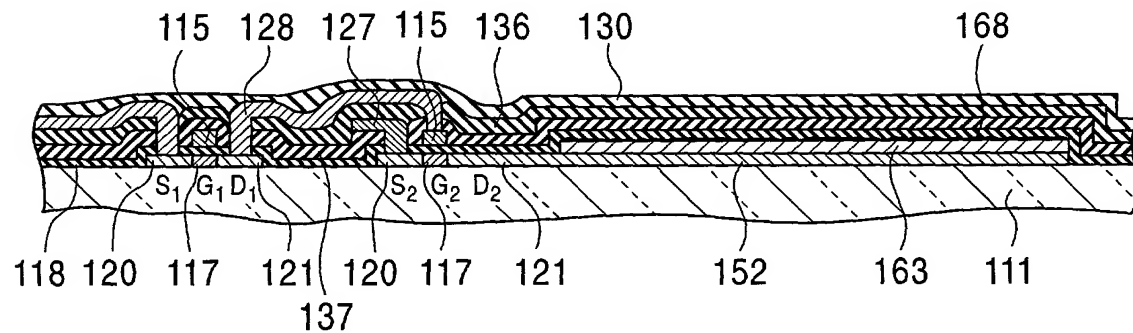


FIG. 26H

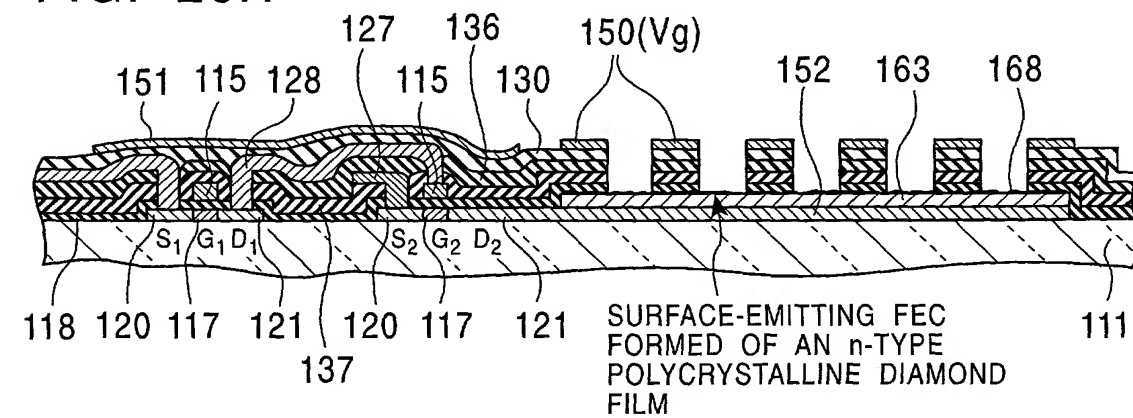


FIG. 27A

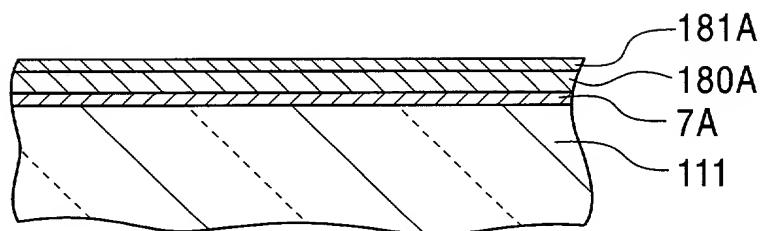


FIG. 27B

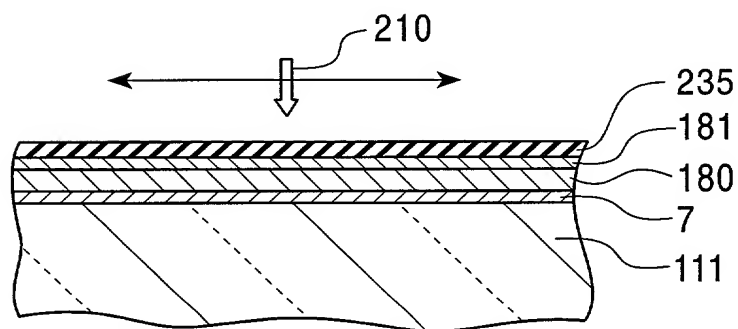


FIG. 27C

